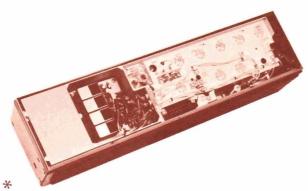


## VASTR Progress Line

406-470 MHz, RECEIVER MODELS 4ER42E10-33 & 4ER42G10-33



#### **SPECIFICATIONS**

FCC Filing Designation

Frequency Range

Audio Output

Sensitivity

12-dB SINAD (EIA Method) 20-dB Quieting Method

Intermodulation (EIA)

Selectivity

EIA Two-Signal Method 20-dB Quieting Method

Spurious Response

First Oscillator Stability

Type ER-42-E Receivers Type ER-42-G Receivers

Modulation Acceptance

Squelch Sensitivity

Critical Squelch Standard Receiver UHS Receiver Maximum Squelch

Maximum Frequency Separation

Frequency Response

#### ER-42-E & G

406-420 & 450-470 MHz

5 watts at less than 5% distortion

Standard Receiver	Ultra-High Sensitivity Receive	
0.35 μV	0.20 μV	
0.50 μV	0.25 μV	
-75 dB	-70 dB	

-85 dB (adjacent channel, 25 kHz channels) -100 dB at ±20 kHz

-100 dB

 $\pm .0005\%$  (-30°C to +60°C) +.0002% (-30°C to +60°C)

 $\pm 7.5$  kHz

0.2 μV 0.15 μV Greater than 20 dB quieting (less than 1.5 µV)

0.4%

+1 and -8 dB of a standard 6-dB per octave deemphasis curve from 300 to 3000 Hz (1000-Hz reference)

<sup>\*</sup>These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

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#### — WARNING —

No one should be permitted to handle any portion of the equipment that is supplied with high voltage; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.

#### DESCRIPTION

General Electric MASTR Progress Line Receivers Types ER-42-E & G are double-conversion, superheterodyne FM receivers designed for operation in the 406-420 and 450-470 megahertz bands. The Type ER-42-E Receivers contain a standard oscillator with a frequency stability of  $\pm 0.0005\%$ , while the Type ER-42-G Receivers contain an Integrated Circuit Oscillator Module (ICOM) with a frequency stability of  $\pm 0.0002\%$ . Standard and ultra-high sensitivity (UHS) versions are available for both types.

The receivers are of single-unit construction and are completely housed in an aluminum casting for maximum shielding and rigidity. The top part of the casting contains the front end through the 1st low IF amplifier stages. The bottom portion of the casting contains the audio squelch board and the optional Channel Guard encoder-decoder board.

#### **CIRCUIT ANALYSIS**

The MASTR Progress Line Receiver is completely transistorized, using silicon

transistors throughout for added reliability. Input leads to the receiver are individually filtered by the 20-pin feed-through by-pass connector J443. A regulated +10 volts is used for all receiver stages except the audio PA stage which operates from the 12-volt system supply.

Centralized metering jack J442 is provided for use with General Electric Test Set Models 4EX3A10 or 4EX8K11, for ease of alignment and servicing. The Test Set meters the oscillator, multiplier, and limiter stages as well as the discriminator, and regulated 10 volts.

#### RF AMPLIFIER (A410/A411)

RF Amplifier A410/A411 is used only in ultra-high sensitivity (UHS) receivers and consists of two tuned helical resonators and an RF amplifier (Q1).

The RF amplifier uses a Field-Effect Transistor (FET) as the active device. A FET may be considered a semiconductor current path (or channel) whose resistance is varied by a voltage applied between the "gate" and "source" terminals. Lead identification for the FET is shown in Figure 2A. The FET has voltage-controlled characteristics, and may be compared to a vacuum tube in operation (see Figure 2B).

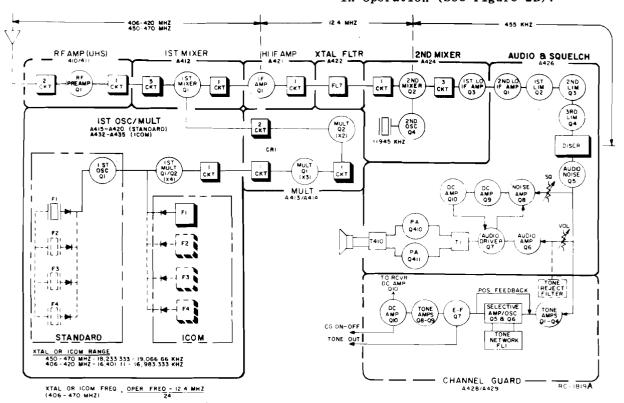


Figure 1 - Receiver Block Diagram

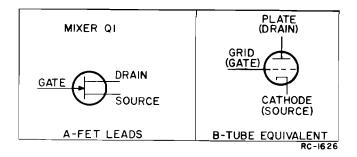


Figure 2 - FET Nomenclature

RF from the antenna is coupled through cable W444 to a tap on L410/L412. The tap is positioned to provide the proper impedance match to the antenna. RF energy is coupled to L411/L413 through an opening in the shield wall, and then to the source terminal of FET Q1.

Ql operates as a grounded-gate amplifier. This method of operation provides a low impedance input to the amplifier. The amplified output is taken from the drain terminal and coupled through a tuned circuit (C7 and L2/L3) to the input of five helical resonators.

#### HELICAL RESONATORS

In receivers without the UHS option, the front end RF selectivity is provided by five tuned helical resonators (L414/L419 through L418/L423). RF cable W441 connects the RF signal from the antenna to a tap on L414/L419. The tap is positioned to provide the proper impedance match to the antenna. The output of L418/L423 is coupled through capacitor C1 to the 1st mixer assembly.

#### 1ST OSCILLATOR AND MULTIPLIER

Receiver Models 4ER42E10-33 are equipped with standard Oscillator/Multiplier Boards A415-A420. Receiver Models 4ER42G10-33 are equipped with Oscillator/Multiplier Boards which use the Integrated Circuit Oscillator Module (ICOM).

#### Standard Oscillator/Multiplier Board (A415-A420)

The oscillator in the standard Oscillator/Multiplier Board is a transistorized Colpitts oscillator. The oscillator crystal operates in a fundamental mode at a frequency of approximately 16 to 19 megahertz. The crystal is cut to provide temperature compensation at the high end of the temperature range and is thermistor compensated at low temperatures. This provides instant warm-up with a frequency stability of ±0.0005% without crystal ovens or warmers.

In single-frequency receivers, a jumper from H1 to H2 connects regulated +10 volts to the crystal circuit. Feedback for the oscillator is developed across C47.

In multi-frequency receivers, a diode is connected in series with the crystal and up to three additional crystal circuits can be added. The 10-volt jumper is removed, and the proper frequency is selected by switching the desired crystal circuit to +10 volts by means of a frequency selector switch on the control unit. Switching the +10 volts to the crystal circuit forward biases the diode in series with the desired crystal, and the crystal frequency is applied to the base of oscillator transistor Q1. The oscillator output is coupled through C45 to the base of 1st Multiplier Q2.

The 1st multiplier output is coupled through T1/T2 to Multiplier Board A413/A414. T1/T2 is tuned to four times the crystal frequency. The 1st multiplier stage is metered at J442-4 through metering network C38, CR6, R17 and R18.

#### Oscillator/Multiplier Board With ICOM (A432-A435)

Oscillator/Multiplier Boards A432-A435 uses ICOM Module Model 4EG26A10. The ICOM module consists of a crystal-controlled Colpitts oscillator, a voltage regulator, and a buffer output stage. The entire module (including crystal) is enclosed in a dust-proof aluminum can, with the ICOM frequency and the receiver operating frequency printed on the top. Access to the oscillator trimmer is obtained by prying off the plastic GE decal on the top of the can.

The oscillator frequency is temperature-compensated at both ends of the temperature range to provide instant frequency compensation, with a frequency stability of  $\pm 0.0002\%$  without crystal ovens or warmers.

In single-frequency receivers, +10 volts for operating the ICOM is obtained by a jump-er from H1 to H2. With the ICOM operating, diode CR1 is forward biased and the oscillator output is applied to the 1st multiplier Q1.

The 1st multiplier output is coupled through T1/T2 to multiplier board A413/A414. T1/T2 is tuned to four times the ICOM frequency. The 1st multiplier stage is metered at J442-4 through metering network C4, CR5, R5 and R6.

In multi-frequency receivers, up to three additional ICOM modules can be plugged into the board. The 10-volt jumper is removed and the proper frequency is selected by switching the desired ICOM to +10 volts by means of a frequency selector switch on the control unit.

#### —— CAUTION ——

All ICOM modules are individually compensated at the factory, and cannot be repaired in the field. Any attempt to remove the ICOM cover will void the warranty.

#### MULTIPLIER BOARD (A413/A414)

Following the oscillator board are two multiplier stages. A413-Q1 operates as a tripler, and Q2 operates as a doubler. Q2 is metered at J442-1 across metering resistor R6.

The output of Q2 is coupled through two helical resonator circuits to the source terminal of the 1st mixer. The helical resonators are tuned to six times the 1st multiplier output for a total multiplication of 24 times the crystal frequency.

#### 1ST MIXER (A412)

The 1st Mixer uses a Field-Effect Transistor (FET) as the active device (Fig. 2). The FET mixer has several advantages over a conventional transistor mixer, including a high input impedance and an output that is relatively free of harmonics (low in intermodulation products).

RF from the helical resonators is applied to the gate of Ql, and injection voltage from the multiplier is applied to the source. The mixer output is taken from the drain with the output tuned to the 12.4 MHz high IF frequency.

#### HI IF AMPLIFIER (A421) AND CRYSTAL FILTER (A422)

A series-resonant circuit (A412-L2 and -C3) couples the mixer output to the emitter of the high IF amplifier A421. The transistor is connected as a grounded-base amplifier which provides a low impedance for the mixer input. The amplifier output is coupled through transformer Tl to the crystal filter.

Highly-selective crystal filter A422 provides the major selectivity for the receiver. The output of the filter is coupled through impedance-matching transformer A424-T2 to the base of the 2nd mixer.

#### 2ND OSCILLATOR, 2ND MIXER AND 1ST LO IF AMPLIFIER (A424)

A424-Q4 operates in a Colpitts oscillator circuit, with feedback supplied through C18. The oscillator low-side injection voltage (11,945 kHz) is applied to the base of the 2nd mixer.

The High IF signal from the filter and the injection voltage from the 2nd oscillator is applied to the base of 2nd mixer Q2. The 445-kHz mixer output is applied to three tuned low IF circuits, L1, L2 and L3. These tuned circuits are required for shaping the nose of the IF waveform, and for rejecting any undesired output frequencies from the 2nd mixer.

The low IF signal is applied to the base of 1st low IF amplifier Q3. The output of Q3 is R-C coupled to the base of the 2nd low IF amplifier.

#### 2ND LO IF AMPLIFIER AND LIMITERS (A426)

Additional amplification of the low IF signal going to the limiter stages is provided by 2nd low IF amplifier A426-Q1. This stage is metered at J442-2 through a metering network consisting of C19, CR3 and R25.

Following the 2nd low IF amplifier are three R-C coupled limiter stages (A426-Q2, -Q3 and -Q4). The 1st limiter is metered at J442-3 through metering network C20, CR4 and R26.

#### DISCRIMINATOR (A426)

The limiter output is applied to a Foster-Seely type discriminator, where diodes CRl and CR2 rectify the 455-kHz signal to recover the audio. The discriminator is metered at J442-10 through metering network Cl6 and R23.

#### AUDIO - NOISE AMPLIFIER (A426)

The discriminator output is coupled through a low-pass filter (C16, C18, R21 and R22) to the base of audio-noise amplifier Q5. The filter removes any 455-kHz signal remaining in the discriminator output. Q5 operates as a emitter-follower to match the discriminator impedance to the VOLUME control, SQUELCH control, and Channel Guard input. The stage also provides power gain.

#### AUDIO AMPLIFIERS (A426)

Any audio present in the incoming signal is coupled from the emitter of Q5 through the VOLUME control and a de-emphasis network to the base of audio amplifier Q6. The de-emphasis network consists of C22, C23, R30 and R31.

Audio driver Q7 follows the audio amplifier. The audio output of Q7 is coupled through transformer T1 to provide phase inversion for the push-pull audio PA stage.

Q410 and Q411 operate as a push-pull Class AB audio PA stage. The PA output is coupled through audio transformer T410 to the loudspeaker. The yellow and white tertiary windings of T410 supply balanced feedback to the collector of Q7. The feedback winding minimizes distortion and prevents the pick-up of external electrical noise.

Base bias for the PA stage and the elimination of crossover distortion is controlled by bias adjust potentiometer R43. The potentiometer is set at the factory as shown in STEP 1 of the receiver Test Procedure.

\_\_\_\_\_ NOTE \_\_\_\_

Do not adjust bias adjust potentiometer R43 unless PA transistors Q410 and Q411 have been replaced.

Audio high and low are also present at centralized metering jack J442, and can be used as shown in STEP 1 of the receiver Test Procedure. The output stage provides 5 watts at less than 5% distortion into a 3.5-ohm load at the receiver output terminals (3.2-ohm load at the Control Unit).

#### SQUELCH (A426)

Noise from the audio-noise amplifier operates the squelch circuit. With no carrier present in the receiver, this noise is coupled to the base of noise amplifier Q8 through a high-pass filter which attenuates frequencies below 3 kHz. The filter consists of C30, C31 and R45, as well as C34 and L3 in the collector circuit of Q8. The gain of Q8 is determined by the Squelch control, which varies the bias on the base of Q8. Thermistor RT2 keeps the critical squelch constant over wide variations in temperature.

The output of noise amplifier Q8 is rectified by diodes CR5 and CR6, and filtered by C36 and C37 to produce a negative DC voltage. This DC voltage is applied to the base of DC amplifier Q9, turning it off. When turned off, the collector voltage of Q9 rises to approximately 8 volts, turning on DC amplifier Q10. When conducting, the collector voltage of Q10 drops to almost ground potential, which removes the base bias to audio amplifier Q6 and audio driver Q7, turning them off.

When the receiver is quieted by a signal (unsquelched), the noise in the receiver is reduced, turning DC amplifier Q9 on and DC amplifier Q10 off. This allows the audio stages to conduct so that sound is heard in the speaker.

Resistor R53 connects from the emitter of audio driver Q7 to the emitter of noise amplifier Q8, providing a hysteresis loop in the squelch circuit. When a weak signal opens the squelch, the signal level may be reduced by 4 to 6 dB without the squelch closing. This limits squelch "flutter" or "picket-fence" operation.

With audio driver Q7 conducting, a positive voltage through R53 helps to reduce the gain of noise amplifier Q8. This positive feedback provides a quick, positive switching action in the squelch circuit. When the receiver squelches, audio driver Q7 turns off and its emitter potential drops to zero. This reduces the DC feedback through R53 to the emitter of noise amplifier Q8. Reducing the feedback causes Q8 to conduct harder, turning the audio stages off quickly.

Keying the transmitter removes the  $\pm 10$  volts from J19, turning off DC amplifier Q9 and turning on Q10 to mute the receiver.

#### CHANNEL GUARD (A428/A429)

Channel Guard Board Model 4EK16Al0 is a fully transistorized encoder-decoder for use in the MASTR Professional Series mobile and station combinations. The tone frequencies are controlled by plug-in tone networks that are made with precision components for excellent stability and reliability. The tone frequencies range from 71.9 to 203.5 Hz.

#### Encoder (A428)

Keying the transmitter removes the receiver mute +10 volts, and forward biases feedback control diode CR5, causing it to conduct. When conducting, the diode shunts R39 which reduces the impedance of the positive feedback loop (R39, R35 and C19). This provides the necessary gain to the base of Q5 to permit oscillation.

The encoder tone is provided by selective amp-oscillator transistors Q5 and Q6 which oscillate at a frequency determined by the tone network. Negative feedback applied through the tone network to the base of Q5 prevents any gain in the stage except at the desired encode frequency.

Starting network R45, C21, C22 and CR6 provide an extremely fast starting time for the encoder tone. Keying the transmitter removes the receiver mute +10 volts, causing a pulse to be applied to the base of Q6 to quickly start the oscillator. Thermistorresistor combination R32 and RT1 provides temperature compensation for the oscillator output. Limiter diodes CR3 and CR4 keep the tone amplitude constant.

Emitter-follower Q7 follows the oscillator circuit. The encoder tone is taken from the emitter of Q7 and applied to an

active low-pass filter (G101) on the transmitter.

#### Decoder (A428)

The decoder function is designed to eliminate all calls that are not tone coded for the Channel Guard frequency. As long as the CHANNEL GUARD-OFF switch on the control unit is left in the CHANNEL GUARD position, all signals are locked out except those from transmitters that are continuously tone coded for positive identification by the receiver.

Placing the CHANNEL GUARD-OFF switch in the OFF position instantly disables the Channel Guard operation so that all calls on the channel can be heard. When the hookswitch option is used, lifting the microphone from its hanger disables the Channel Guard Circuit.

Audio, tone and noise are taken from the emitter of the receiver audio-noise amplifier A426-Q5 and is fed through A428-J1 to four tone amplifier and bandpass filter circuits. The filters remove the audio and high-frequency noise from the signal, and the tone amplifiers provide sufficient gain to insure clipping by limiter diodes CR1 and CR2. The clipping action eliminates variation in the squelch performance due to changes in tone deviation. The signal is then applied to selective amplifiers Q5 and Q6 which amplify only the tone determined by the tone network.

The output of the selective amplifier is applied through emitter-follower Q7 to the high gain, broad-band tone amplifiers Q8 and Q9. The output of Q9 is rectified by detector diodes CR7 and CR8, and the resulting negative DC voltage controls the squelch gate. Q8 is normally biased for low gain. Then the tone is detected by CR7 and CR8, feedback is provided through R54 to quickly change the bias on Q8 for full gain. This ensures a more positive "unsquelching" action.

Squelch gate diode CR9 is normally forward biased by a positive DC voltage (approximately 1.5 volts) fed through R58. The forward bias causes CR9 to conduct, feeding a DC voltage to the base of DC amplifier A426-Q10 in the receiver. This removes the bias on the receiver audio stages and holds them off.

When the proper tone is applied to the decoder, the negative DC voltage from the detector diodes back-biases squelch gate diode CR9 and cuts off the positive bias to the receiver DC amplifier A426-Q10. However, the receiver noise squelch circuit continues to operate until a carrier quiets the receiver.

Placing the CHANNEL GUARD - OFF switch in the OFF position (or removing the microphone from its hookswitch) removes the ground to the base of the decoder DC switch (Q10), causing it to conduct. This back-biases squelch control diode CR9 and cuts off the positive bias to the receiver DC amplifier (A426-Q10). The receiver noise squelch circuit continues to operate until a carrier quiets the receiver.

A tone rejection filter connected in parallel with A426-J2 (in the receiver bypasses any incoming tone to ground. This attenuates the tone level reaching the receiver audio circuits. The filter is composed of C26, C27, C28, C29, L1 and R59.

An optional tone reject filter (A429) that is identical to the filter described above is available for use in two-way radios with transmitter Channel Guard only.

#### MAINTENANCE

#### DISASSEMBLY

To service the receiver from the top-

- Pull locking handle down and pull radio about one inch out of mounting frame. (see Fig. 3).
- 2. Pry up cover at rear of receiver.
- 3. Slide cover back and lift off.

To service the receiver from the bottom-

- 1. Pull locking handle down. Pull radio out of mounting frame. (see Fig. 4).
- Remove screws in bottom cover. Pry up cover at back of receiver.
- 3. Slide cover back and lift off.

To remove the receiver from the system frame—

- Loosen the two Phillips-head retaining screws in front casting (see Figure 3), and pull casting away from system frame.
- Remove the four screws in the back cover.
- Remove the two screws holding the receiver at each end of the system frame.
- 4. Disconnect the antenna jack and the 20pin connector from the front of the receiver, and slide the unit out of the system frame.

LBI-3999 MAINTENANCE

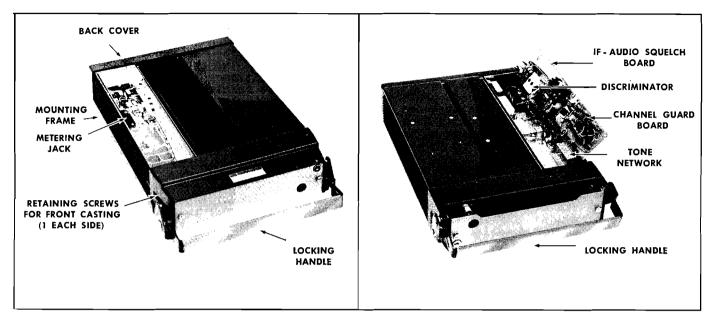


Figure 3 - Removing Top Cover

Figure 4 - Removing Bottom Cover

#### COMPLETE RECEIVER ALIGNMENT

1.

PF

1.

2

3

4

ΑI

#### EQUIPMENT REQUIRED

- GE Test Set Models 4EX3A10, 4EX8K11, station test meter panel, or 20,000 ohms-per-volt multimeter.
- 2. A 450 to 460 kHz source (GE Test Set Model 4EX7AlO), and 406-470 MHz signal source. Connect a one-inch piece of insulated wire no larger than .065 inch to generator output probe.

#### PRELIMINARY CHECKS AND ADJUSTMENTS

- 1. Connect Test Set to receiver centralized metering jack J442, and set meter sensitivity switch to the TEST 1 or 1-volt position.
- 2. For a large change in frequency or a badly mis-aligned receiver, set crystal trimmer C9 on 1st OSC/MULT board (ER-42-E only) to mid-capacity. In multi-frequency receivers, set C10, C11 or C12 to mid-capacity as required.
- 3. In multi-frequency receivers where the maximum frequency spacing is less than 500 kHz, align the unit on channel F1. If the frequency spacing is greater than 500 kHz, align the receiver on the center frequency.
- 4. With Test Set in position J, check for regulated +10 volts. If using Multimeter, measure from C425 to C426.
- 5. If using Multimeter, connect the positive lead to J442-16 (ground).
- 6. Disable the Channel Guard.

#### ALIGNMENT PROCEDURE

	METERING	POSITION			
STEP	GE Test Set or Meter Panel	Multimeter	TUNING CONTROL	METER READING	PROCEDURE
				DISCRIMINATOR	
1.	A (DISC)	Pin 10	L1 and L2 (on IF-AUDIO SQUELCH board)	Zero	Remove three screws and swing open the IF-AUDIO & SQUELCH board. Adjust L1 (disc primary) 1/2 turn counterclockwise from the bottom of coil. Next, apply a 455-kHz signal to J2 and J4 and adjust L2 (disc secondary) for zero meter reading.
2.	A (DISC)	Pin 10		See Pro- cedure	Alternately apply a 450-kHz and 460-kHz signal and check for reading of at least 0.3 volt, but not more than 0.5 volt on GE Test Set, Both readings must be within .05 volt. Do not attempt to balance reading any closer than 0.05 volt.
			OSCILL	ATOR AND MULTIF	PLIERS
3.	D (MULT-1)	Pin 4	L5 (1st OSC/MULT) and L1 (2nd MULT)	See Pro- cedure	Tune L5 for maximum meter reading. Them tune L1 for minimum meter reading.
4.	G (MULT-1)	Pin 4	L5 (1st OSC/MULT) and L1 and L2 (2nd MULT)	Maximum	Tune L5, $L1$ and $L2$ for maximum meter reading. If two peaks occur while tuning $L1$ and $L2$ , use the peak with the slug nearest the top of the coil.
5.	G (MULT-2)	Pin 4	C423	See Pro- cedure	Adjust C423 for a small dip in meter reading.
6.	A (DISC)	Pin 10		Zero	Apply an on-frequency signal into Hole 411. Adjust the signal generator for discriminator zero.
7.	B (2nd IF AMP)	Pin 2	C423 and C424	Maximum	Apply an on-frequency signal as above. Tune C423 and C424 for maximum meter reading, keeping signal below saturation.
				RF SELECTIVITY	
8.	B (2nd IF AMP)	Pin 2	L3 (1st Mixer)	Maximum	Apply an on-frequency signal in Hole 411 and tune L3 for maximum meter reading. If two peaks occur, use the peak with the slug nearest the bottom of the coil.
9.	B (2nd IF AMP)	Pin 2	C415 thru C418	Maximum	Apply an on-frequency signal in the Hole shown below, keeping the signal below saturation. Tune C415 thru C418 for maximum meter reading as shown below:
					Insert Generator Probe In: Peak
					1. Hole 411 C417
					2. Hole 410 C415, C416 thru C417
10.	B (2nd IF AMP)	Pin 2	C414 thru C418, L3 (on 1st Mixer) and C410, C411 and C7 (on UHS receivers)	See Pro- cedure	Apply an on-frequency signal to the receiver antenna jack. Tune C410, C411 and C7 on UHS receivers for maximum meter reading. On all receivers, tune C414 for maximum meter reading, and tune C415 thru C418 and L3 for maximum quieting.

#### 2ND MIXER & HI IF

The 2nd mixer, and high IF circuits have been aligned at the factory and will normally require no further adjustment. If adjustment is necessary use the procedure outlined in STEPS 11, 12 and 13.

- NOTE -

Refer to DATAFILE BULLETIN 1000-6 IF Alignment of Two-Way Radio FM Receivers for helpful suggestions on how to determine when IF alignment is required.

11.	B (2nd IF AMP)	Pin 2	L3, L2, L1, T2 (2nd Mixer) and T1 (Hi IF AMP)	Maximum	Apply on-frequency, unmodulated signal and tune L3, L2, L1, T2 (2nd mixer) and T1 (Hi IF AMP) for maximum meter reading, keeping signal below saturation.
12.			L3, L2, L1, T2 (2nd Mixer) and T1 (Hi IF AMP)		Connect scope, signal generator, and detector as shown in Figure 7. Set signal generator level for 30-50 $\mu v$ and modulate with 10 kHz at 20 Hz. With detector at the collector of Q3 (2nd mixer board output), tune for double trace as shown on scope pattern.
13.	A (DISC)	Pin 10		See Pro- cedure	Check to see that discriminator idling voltage in within $\pm .06$ volt of zero with no signal applied. Check to see that modulation acceptance bandwidth is between $\pm 7.5$ and 9 kHz.

14. Refer to the appropriate adjustment procedure for the ICOM or Standard Oscillator.

#### FRONT END ALIGNMENT

#### EQUIPMENT REQUIRED

- GE Test Set Model 4EX3A10, 4EX8K11 station test meter panel or 20,000 ohms-per-volt multimeter.
- A 406-470 MHz signal source. Connect a one-inch piece of insulated wire no larger than 0.065 inch to generator output probe.

#### PRELIMINARY CHECKS AND ADJUSTMENTS

- Connect Test Set to receiver centralized metering jack J442 and set meter sensitivity switch to the TEST 1 (or 1-volt position on 4EX8K11).
- With Test Set in position J, check for regulated +10 volts. If using Multimeter, measure from C425 to C426.
- 3. If using Multimeter, connect the positive lead to J442-16 (ground).
- 4. Disable the Channel Guard.

#### ALIGNMENT PROCEDURE

	METERING PO	SITION	1		
STEP	GE Test Set or Meter Pane	Multimeter - at J442	TUNING CONTROL	METER READING	PROCEDURE
	or meter rune	<del></del>	FOR AND MULTIPLIERS		
1.	D (MULT-1)	Pin 4	L5 (1st OSC/MULT) and L1 (2nd MULT)	See Pro- cedure	Tune L5 for max- imum meter read- ing. Then tune L1 for minimum meter reading.
2.	G (MULT-2)	Pin 4	L5 (1st OSC/MULT) and L1 and L2 (2nd MULT)	Maximum	Tune L5, L1 and L2 for maximum meter reading. If two peaks occur while tuning L1 and L2, use the peak with the slug mearest the top of the coil.
3,	G (MULT-2)	Pin 4	C423	See Pro- cedure	Adjust C423 for a small dip in meter reading.
4.	A (DISC)	Pin 10		Zero	Apply on on-frequency signal into Hole 411. Adjust the signal generator for discriminator zero.
5.	B (2nd IF AMP)	Pin 2	C423 and C424	Maximum	Apply an on-frequency signal as above. Tune C423 and C424 for maximum meter reading, keeping signal below saturation.
		R	F SELECTIVITY		
6.	B (2nd IF AMP)	Pin 2	L3, C415-C418	Maximum	Apply an on-frequency signal in Hole 411 and tune L3 and C415 thru C418 for maximum meter reading, keeping the signal below saturation. If two peaks occur when tuning L3, use the peak with the slug nearest the bottom of the coil.
7.	B (2nd JF AMP)	, Pin 2	C414 thru C418, L3 (on 1st Mixer) and C410, C411 and C7 (on UMS receivers)	See Pro- cedure	Apply on on-frequency signal to the receiver antenna jack. Tune C410, C411 and C7 on UHS receivers for maximum meter reading. On all receivers, tune C414 for maximum meter reading, and then tune C41 thru C418 and L3 for maximum quiet ing.
		FREG	UENCY ADJUSTMENT		1
					or Standard

RG-58/U CABLE SOLDER (KEEP LT)

CONNECTOR (TO COUNTER)

4 TURE INSUL

C9 F1

Figure 5 - Coaxial Cable and Te:

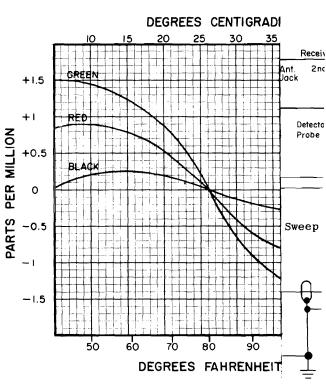
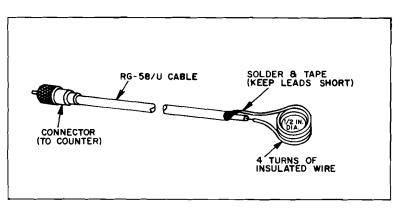
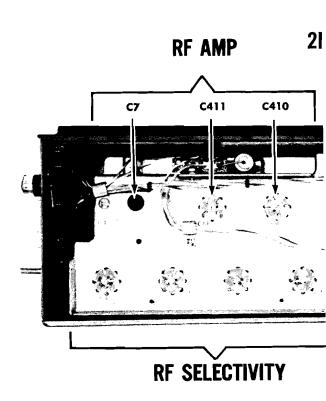


Figure 6 - ICOM Correction C

 $lignm\epsilon$ 



 $$\operatorname{RC}\text{-}1600$$  Figure 5 - Coaxial Cable and Test Loop



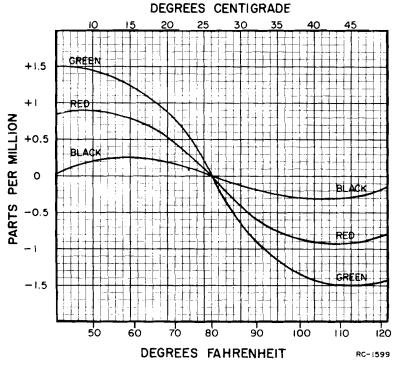
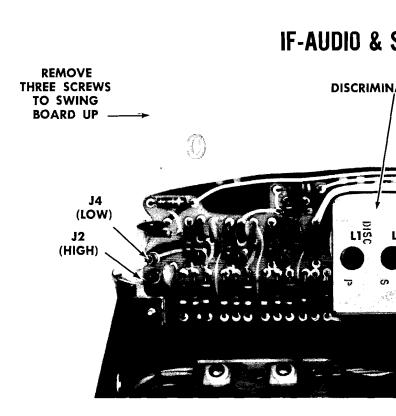
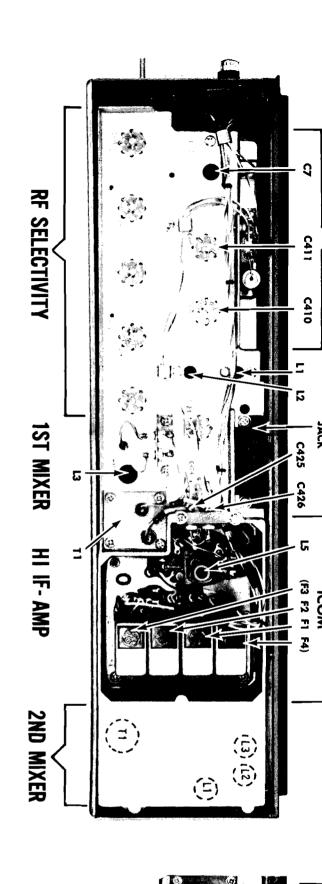
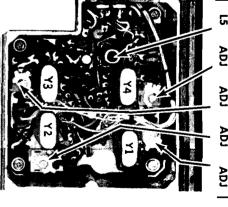


Figure 6 - ICOM Correction Curves





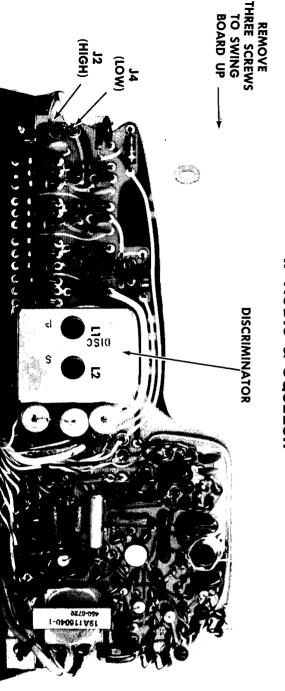


4EX3A10

meter -at J442 Pin 10

(Disc)

# IF-AUDIO & SQUELCH



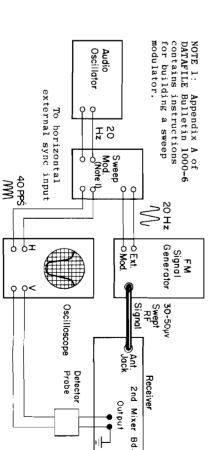
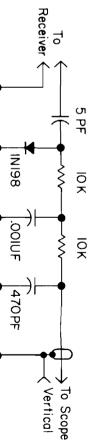


Figure 7 - Test Setup for 20-Hz Double-Trace Sweep Alignment



## ICOM MODULE

Due to the high st ed that zero discrimina oscillator frequency. in the following proced

## EQUIPMENT REQUIRED:

- 1. Frequency Counter
   range. (The count
   million.)
- 2. Coaxial cable with
- 3. Mercury thermomete

### PROCEDURE:

- 1. Check the ICOM tem
- 2. Connect the frequent the 4-turn test lo
- 3. If the ICOM temper: quency indication c stenciled on the IC to obtain this free
- 4. If the temperature range, use the corfrequency as follow
- a. Check the color ing curve to dellion (PPM).
- b. Multiply the free multiply this for observing the so
- c. The frequency me quired) to obta:
- Ambient 7 Correctic (From Fig ICOM Frec
- Set the 1

Multiply (72.933 % Multiply (18,23335

- 72.93333**2**  .00008**4** 72.9332**4**

#### FREQUENCY ADJUSTMENT

#### STANDARD OSCILLATOR

METERING POSITION		TUNING METER		PROCEDURE	
4EX3A10	Multi- meter -at J442	CONTROL READING			
A (Disc)	Pin 10	C9 (on lst OSC/ MULT) C10, C11 and C12 for multi- frequency	Zero	Apply an on-frequency signal to the antenna jack. Tune C9 for zero discriminator reading. In multi-frequency units, tune C10, C11 or C12 as required.	

#### ICOM MODULE

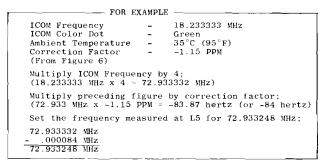
Due to the high stability of the ICOM module, it is not recommended that zero discriminator be used as the indication for setting the oscillator frequency. Instead, measure the ICOM frequency as described in in the following procedure.

#### EQUIPMENT REQUIRED:

- Frequency Counter capable of measuring the 70-80 MHz frequency range. (The counter should have an accuracy of 0.4 part-per million.)
- 2. Coaxial cable with test loop as described in Figure 5.
- 3. Mercury thermometer.

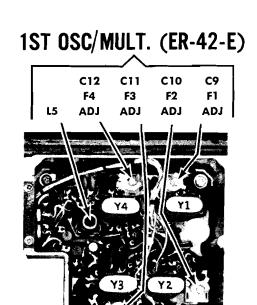
#### PROCEDURE:

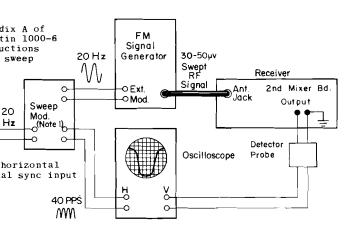
- 1. Check the ICOM temperature by taping the mercury thermometer to the side of the ICOM.
- 2. Connect the frequency counter to L5 (on the lst Osc/Mult) using the 4-turn test loop and cable shown in Figure 5.
- 3. If the ICOM temperature is  $80\,^{\circ}\text{F}$  ( $\pm4\,^{\circ}\text{F}$ ) or  $26.5\,^{\circ}\text{C}$  ( $\pm2\,^{\circ}\text{C}$ ), the frequency indication on the counter should be 4 times the frequency stenciled on the ICOM case. Adjust the ICOM trimmer (if necessary) to obtain this frequency.
- 4. If the temperature is not within the 80°F (±4°F) or 26.5°C (±2°C) range, use the correction curves of Figure 6 for setting the ICOM frequency as follows:
  - a. Check the color dot beneath the GE emblem and select the matching curve to determine the correction factor in parts-per-million (PPM).
  - b. Multiply the frequency stenciled on the ICOM by 4 and then multiply this figure by the correction factor (from Figure 6) observing the sign  $(\pm)$  given to the correction factor.
  - c. The frequency measured at L5 should be 4 times the ICOM frequency  $\pm$  the correction factor. Adjust the ICOM trimmer (if required) to obtain this frequency.



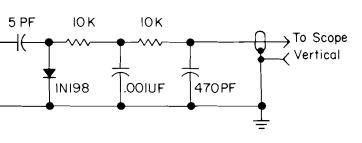
#### ALIGNMENT PROCEDURE

406—470 MHz MASTR RECEIVER MODELS 4ER42E10-45 & 4ER42G10-33





est Setup for 20-Hz Double-Trace Sweep Alignment



e 8 - Detector Probe for Sweep Alignment

a milliammeter in series volt lead at P443-11. With adjust R43 for a reading tely 20 milliamps. This nould not be necessary unat transistor has been re-

Refer to Receiver Troublecedure).

r Alignment (Refer to gnment on reverse side of

#### STEP 2 SENSITIVITY db Sinad)

ecks out properly, measure itivity as follows:

-microvolt, on-frequency ated by 1000 Hz with 3.3-kHz J441.

NGE switch on the Distortion the 200 to 2000-Hz distortion on (1000-Hz filter in the une the filter for minimum ull on the lowest possible 30%, etc.)

NGE switch to the SET LEVEL lter out of the circuit) and nput LEVEL control for a +2 n a mid range (30%).

ng the signal generator outthe RANGE control from SET distortion range until a ence (+2 dB to -10 dB) is ween the SET LEVEL and ange positions (filter out a).

fference (Signal plus Noise on to noise plus distortion "usable" sensitivity level. ity should be less than rated specification with an audio least 2.5 watts (2.9 volts no 3.5-ohm receiver load usportion Analyzer as a VTVM).

F. Leave all controls as they are and all equipment connected if the Modulation Acceptance Bandwidth test is to be performed.

#### **SERVICE CHECK**

If the sensitivity level is more than rated 12 dB SINAD, check the alignment of the RF stages as directed in the Alignment Procedure, and make the gain measurements as shown on the Troubleshooting Procedure.

## STEP 3 MODULATION ACCEPTANCE BANDWITH (IF BANDWITH)

If STEPS 1 and 2 check out properly, measure the bandwidth as follows:

- A. Set the Signal Generator output for twice the microvolt reading obtained in the 12-dB SINAD measurement.
- B. Set the RANGE control on the Distortion Analyzer in the SET LEVEL position (1000-Hz filter out of the circuit), and adjust the input LEVEL control for a +2 dB reading on the 30% range.
- C. While increasing the deviation of the Signal Generator, switch the RANGE control from SET LEVEL to distortion range until a 12-dB difference is obtained between the SET LEVEL and distortion range readings (from +2 dB to -10 dB).
- D. The deviation control reading for the 12-dB difference is the Modulation Acceptance Bandwidth of the receiver. If should be more than ±7.5 kHz (but less that ±9.5 kHz).

#### SERVICE CHECK

If the Modulation Acceptance Bandwidth test does not indicate the proper width, make gain measurements as shown on the Receiver Troubleshooting Procedure.

Г

WS:

Then connect a milliammeter in series with the +12 volt lead at P443-11. With no signal in, adjust R43 for a reading of approximately 20 milliamps. adjustment should not be necessary unless an output transistor has been rereplaced.

F. Leave all equipment Acceptance formed.

equency hertz enna jack

Audio Gain (Refer to Receiver Trouble-G. shooting Procedure).

Η. Discriminator Alignment (Refer to Receiver Alignment on reverse side of page).

If the ser rated 12 dB SIN the RF stages a Procedure, and

shown on the Tr

com J701-2

or from he Distore resistor

nookswitch.

r five-watt

Distortion

according

d, leave

ns. Reading

the receiver

s they are.

zer input

#### STEP 2 **USABLE SENSITIVITY** (12-dB SINAD)

If STEP 1 checks out properly, measure the receiver sensitivity as follows:

- Α. Apply a 1000-microvolt, on-frequency signal modulated by 1000 Hz with 3.3-kHz deviation to J441.
- Place the RANGE switch on the Distortion В. Analyzer in the 200 to 2000-Hz distortion range position (1000-Hz filter in the circuit). Tune the filter for minimum reading or null on the lowest possible scale (100%, 30%, etc.)
- С. Place the RANGE switch to the SET LEVEL position (filter out of the circuit) and adjust the input LEVEL control for a +2 dB reading on a mid range (30%).
- D. While reducing the signal generator output, switch the RANGE control from SET LEVEL to the distortion range until a 12-dB difference (+2 dB to -10 dB) is obtained between the SET LEVEL and distortion range positions (filter out and filter in).
- The 12-dB difference (Signal plus Noise E. and Distortion to noise plus distortion ratio) is the "usable" sensitivity level. The sensitivity should be less than rated 12 dB SINAD specification with an audio output of at least 2.5 watts (2.9 volts RMS across the 3.5-ohm receiver load using the Distortion Analyzer as a VTVM).

#### MODULA BANDW

If STEPS 1 measure the band

- Α. Set the Sig the microvo 12-dB SINAI
- В. Set the RAN Analyzer in Hz filter o the input I ing on the
- C. While incre Signal Gene trol from S until a 12between the readings (f
- D. The deviati 12-dB diffe Acceptance If should b less that ±

If the Modi test does not in gain measuremen Troubleshooting

an 5%, or than five

ecks:

3---low volt-(Refer to or voltages.)

n the clockwise. erly, and low gain. By following the ence of test steps starting with Step 1, defect can be quickly localized. Once

dures, be sure the receiver is tuned and aligned to the proper operating frequency.

#### EST EQUIPMENT REQUIRED

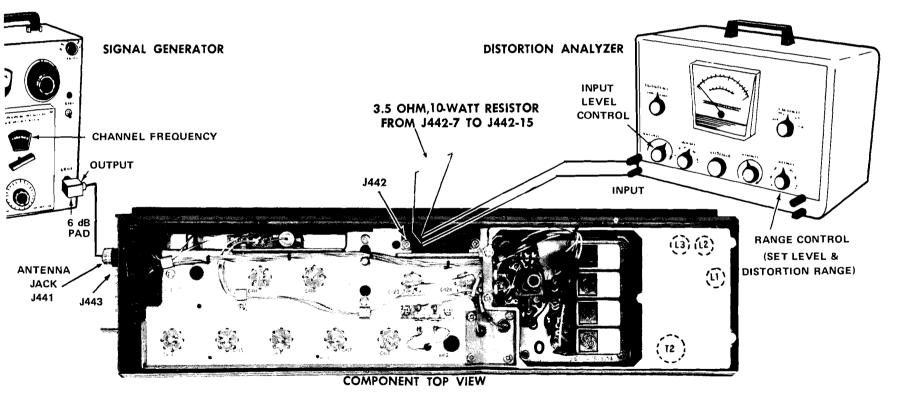
istortion Analyzer similar to: eath IM-12

ignal Generator similar to: easurements M-560

-dB attenuation pad, and 3.5-ohm, 0-watt resistor

#### PRELIMINARY ADJUSTMENTS

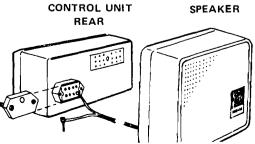
- 1. Connect the test equipment to the receiver as shown for all steps of the receiver Test Procedure.
- 2. Turn the SQUELCH control fully clockwise for all steps of the Test Procedure.
- 3. Turn on all of the equipment and let it warm up for 20 minutes.







REMOVE THREE SCREWS AND SWING BOARD OPEN



#### TEST PROCEDURE

Measure Audio Power Output as follows:

- A. Apply a 1,000-microvolt, on-frequency test signal modulated by 1,000 hertz with ±3.3 kHz deviation to antenna ja J441.
- B. With Five-Watt Speaker:

Disconnect speaker lead pin from J701 (on rear of Control Unit).

Connect a 3.5-ohm load resistor from J442-15 to J442-7. Connect the Distortion Analyzer input across the resist as shown.

OR

#### With Handset:

Lift the handset off of the hookswitch Connect the Distortion Analyzer input from J442-15 to J442-7.

- C. Adjust the VOLUME control for five-wa output (4.18 VRMS using the Distortion Analyzer as a VTVM).
- D. Make distortion measurements according to manufacturer's instructions. Read should be less than 5%. If the receisensitivity is to be measured, leave all controls and equipment as they ar

#### SERVICE CHECK

If the distortion is more than 5%, or maximum audio output is less than fix watts, make the following checks:

- Battery and regulator voltage---low vage will cause distortion. (Refer to Receiver Schematic Diagram for voltagem)
- F. P.A. Bias Adjust (R43) -- Turn the

#### STEP I-QUICKCHECKS

#### **TEST SET CHECKS**

These checks are typical voltage readings measured with GE Test Set Model 4EX3AlO in the Test 1 position, or Model 4EX8KlO or 11 in the 1-volt position.

Metering Position	Reading with No Signal in	Reading with 1 μν unmodulated input
A Disc idling	Less than ±.05 VDC	
B 2nd IF	.05 VDC	0.2 VDC
C 1st Lim	0.6 VDC	0.8 VDC
D Mult 1	1.0 VDC	
G Mult 2	0.3 VDC	
J Regulated +10 Volts	10 VDC	

#### SYMPTOM CHECKS

SYMPTOM	PROCEDURE
NO SUPPLY VOLTAGE	• Check power connections and continuity of supply leads, and check fuse in power supply. If fuse is blown, check receiver for short circuits.
NO REGULATED 10-VOLTS	• Check the 12-volt supply. Then check regulator circuit (See Troubleshooting Procedure for Power Supply).
LOW 1ST LIM READING	• Check supply voltages and then check oscillator reading at J442-4 & 5 as shown in STEP 2A.
	Make SIMPLIFIED VTVM GAIN CHECKS from 2nd Mixer through 1st Limiter stages as shown in STEP 2A.
LOW OSCILLATOR/MULTI- PLIER READINGS	• Check alignment of Oscillator (Refer to Front End Alignment Procedure).
	$\bullet$ Check voltage readings of 1st Oscillator/Multiplier Q1/Q2.
	• Check crystal Y1.
LOW RECEIVER SENSITIVITY	• Check Front End Alignment (Refer to Receiver Alignment Procedure).
	• Check antenna connections, cable and relay.
	• Check 1st and 2nd Oscillator injection voltage.
	• Check voltage readings of RF Amp, 1st Mixer and HI IF Amp.
	• Make SIMPLIFIED GAIN CHECKS (STEP 2A).
LOW AUDIO	• Check Audio PA (Q410 & Q411) voltage readings on schematic diagram.
	<ul> <li>Make simplified gain and waveform checks of audio and squelch stages (Steps 2A and 2B).</li> </ul>
	<ul> <li>Make unsquelched voltage readings in Audio section (Refer to Receiver Schematic Diagram).</li> </ul>
	• Check voltage readings on Channel Guard board.
HIGH DISTORTION AT LOW AUDIO LEVELS (50 MW)	<ul> <li>Set PA bias adjust R43 as specified under Service checks in STEP 1 of TEST PROCEDURES.</li> </ul>
IMPROPER SQUELCH OPERATION	Check voltage readings of Squelch circuit (Refer to Receiver Schematic Diagram).
	<ul> <li>Make gain and waveform checks of audio and squelch stages (Steps 2A and 2B).</li> </ul>
DISCRIMINATOR IDLING TOO FAR OFF ZERO	• See if discriminator zero is in center of IF bandpass.

#### STEP 3-VOLTAGE RATIO READ

#### EQUIPMENT REQUIRED:

- RF Voltmeter (Similiar to Boonton Model 9 Millivac Type MV-18 C).
- Signal on receiver frequency (below sature Correct frequency can be determined by zethe discriminator. Use 1,000 Hertz signals. 3.3 kHz deviation for audio stage.

#### PROCEDURE

- 1. Apply probes to input of stage and system tive (-10 VDC). Take voltage reading (E)  $\,$
- Move probes to input of following stage a system negative. Take reading (E<sub>2</sub>).
- Convert readings by means of the following mula;

Volatge Ratio = 
$$\frac{E_2}{E_1}$$

 Check results with typical voltage ratios on diagram.

#### P 3-VOLTAGE RATIO READINGS -

MENT REQUIRED:

RF Voltmeter (Similiar to Boonton Model 91-CA or Millivac Type MV-18 C).

Signal on receiver frequency (below saturation). Correct frequency can be determined by zeroing the discriminator. Use 1,000 Hertz signal with 3.3 kHz deviation for audio stage.

DURE

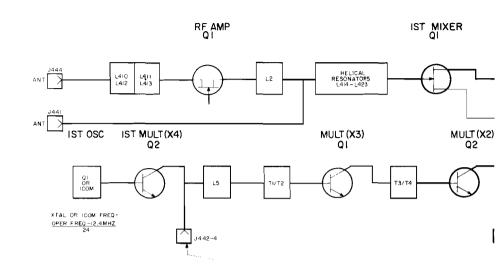
Apply probes to input of stage and system negative (-10 VDC). Take voltage reading (E $_1$ ).

Move probes to input of following stage and system negative. Take reading (E $_2$ ).

Convert readings by means of the following formula:

Volatge Ratio = 
$$\frac{E_2}{E_1}$$

Check results with typical voltage ratios shown on diagram.



- 406-470 MHZ

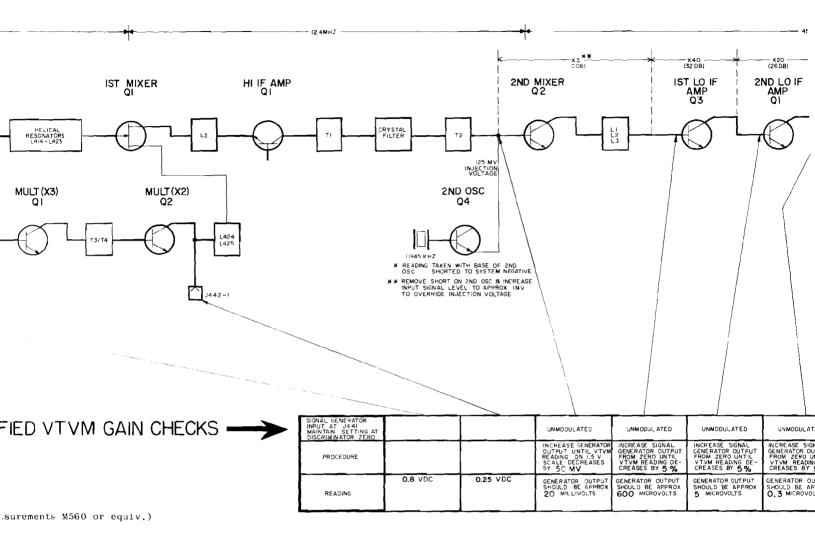
#### STEP 2A-SIMPLIFIED VTVM GAIN CHEC

EQUIPMENT REQUIRED:

- 1. VTVM-AC & DC
- 2. Signal Generator (measurements M560 or equiv.)

#### PRELIMINARY STEPS:

- 1. Set VOLUME control for 4.18 volts across 3.5-ohm load. If this cannot be obtained, set to approx. 70% of max. rotation.
- 2. Set SQUELCH control fully counterclockwise.
- 3. Receiver should be properly aligned.
- Connect VTVM between system negative and points indicated by arrow (except for 1st MULT which references chassis ground).



r 4.18 volts across 3.5-ohm be obtained, set to approx.

ully counterclockwise.

operly aligned.

system negative and points keept for 1st MULT which bund).

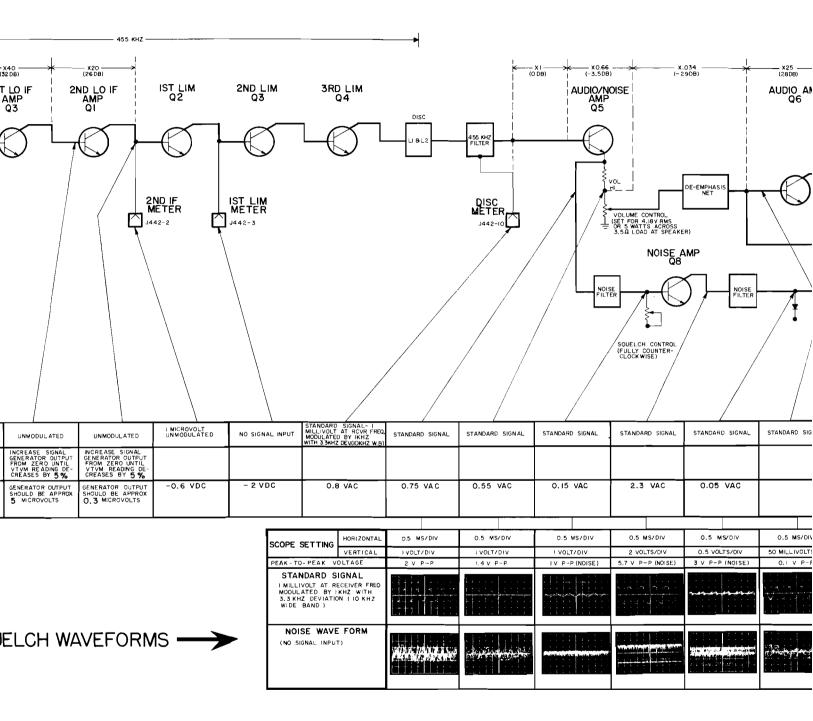
#### STEP 2B-AUDIO & SQUELCH WAVEFOR

#### EQUIPMENT REQUIRED:

- 1. Oscilloscope.
- 2. Signal generator (measurements M560 to equivale

#### PRELIMINARY STEPS:

- Set VOLUME control for 4.18 volts across 3.5-oh load. If this cannot be obtained, set to appro 70% of max. rotation.
- 2. Set SQUELCH control fully counterclockwise.
- 3. Receiver should be properly aligned.
- Connect oscilloscope between system negative an points indicated by arrow.



ents M560 to equivalent).

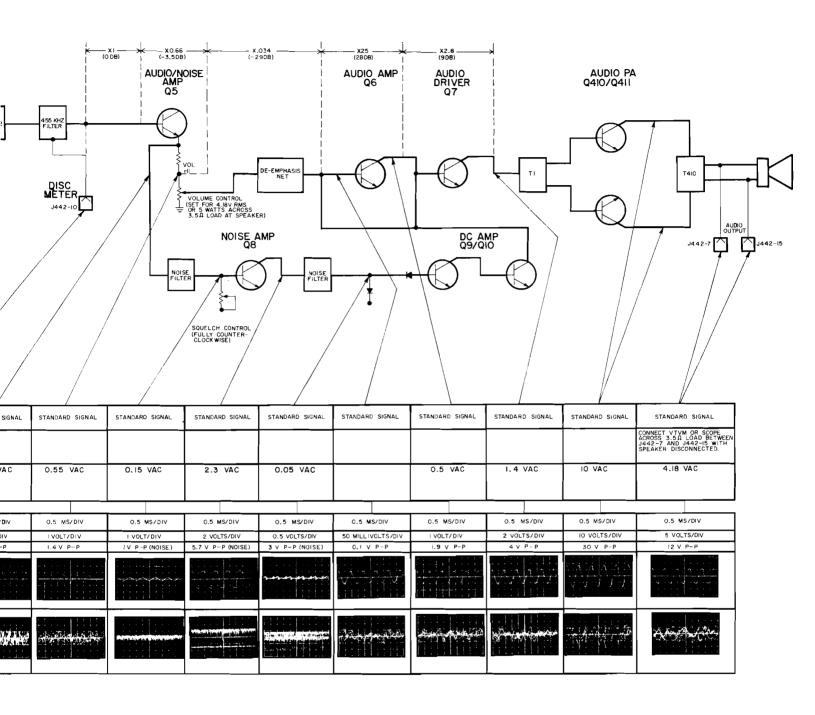
RC-1828 B

B volts across 3.5-ohm otained, set to approx.

counterclockwise.

aligned.

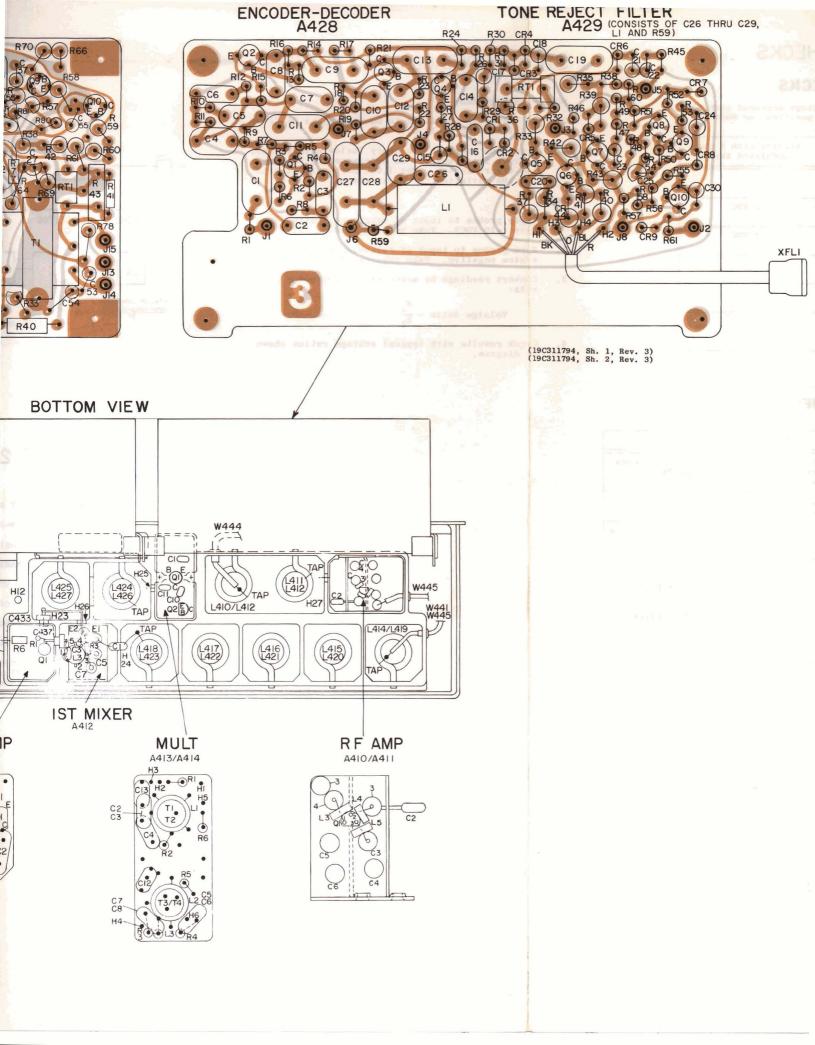
en system negative and

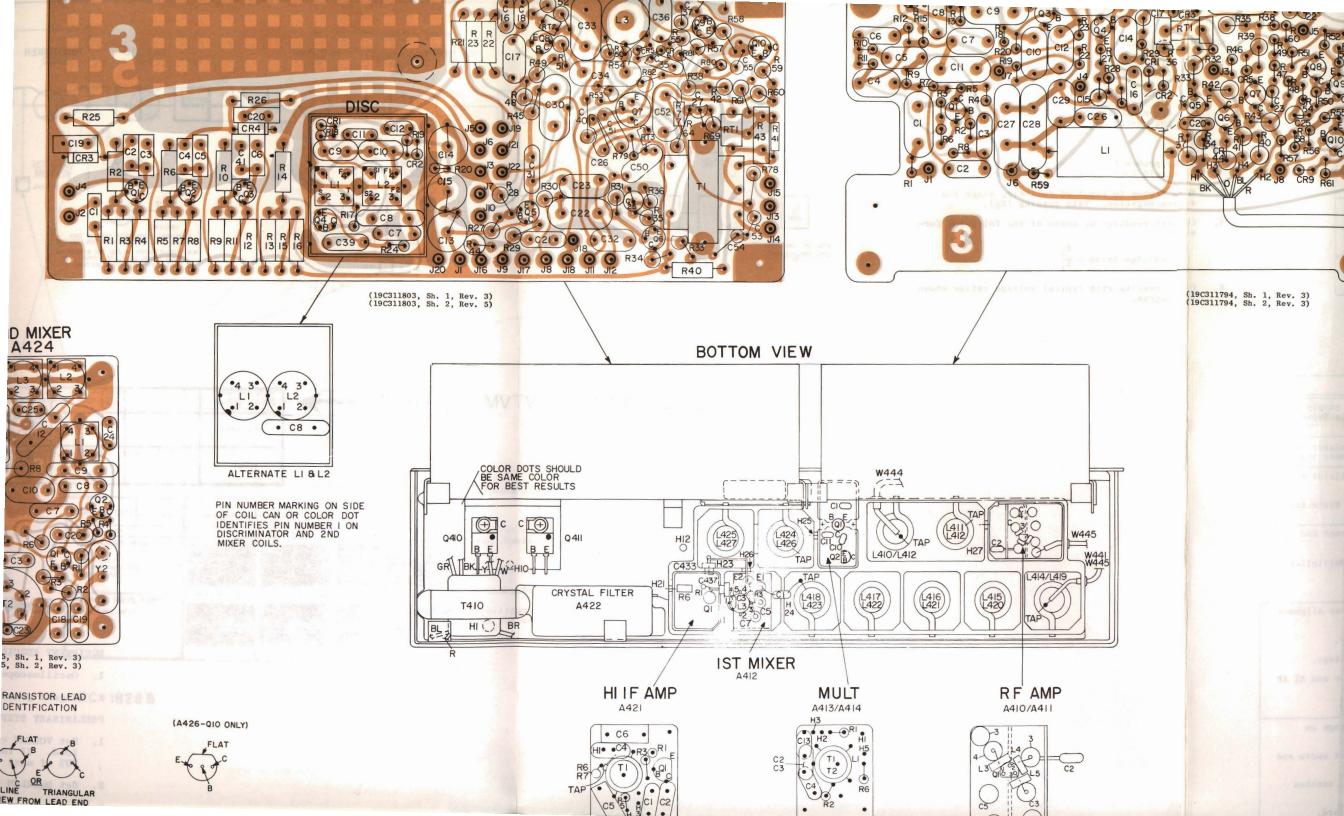


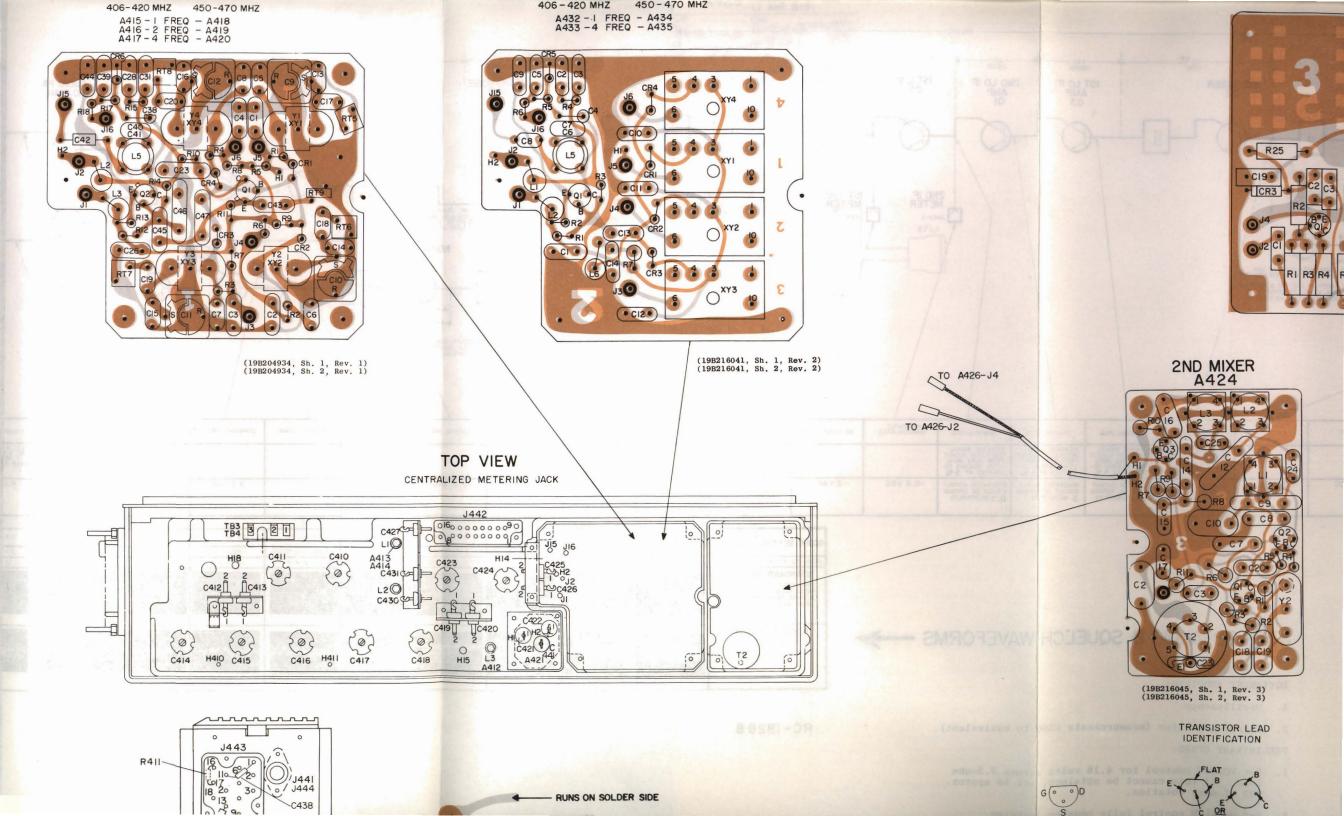
#### TROUBLESHOOTING PROCEDURE

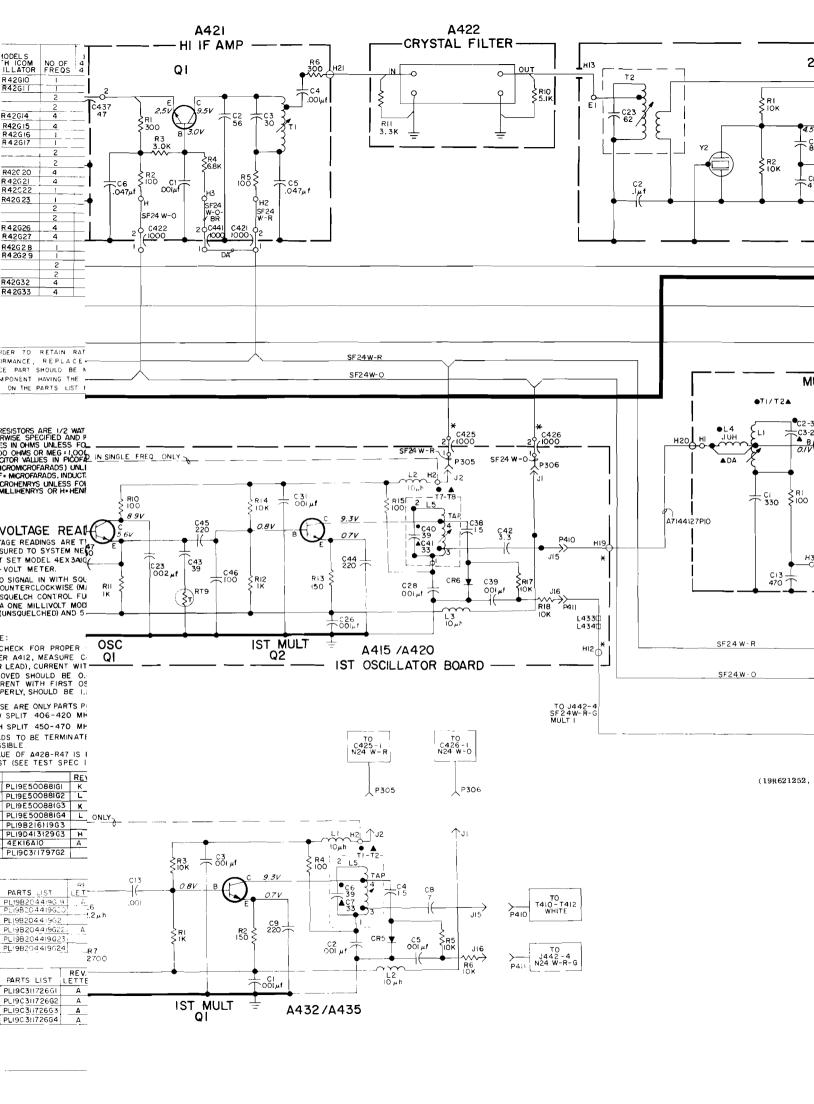
 $\begin{array}{c} 406 - 470 \text{ MHz RECEIVER} \\ \text{MODELS } 4\text{ER42E10-33} \& 4\text{ER42G10-33} \end{array}$ 

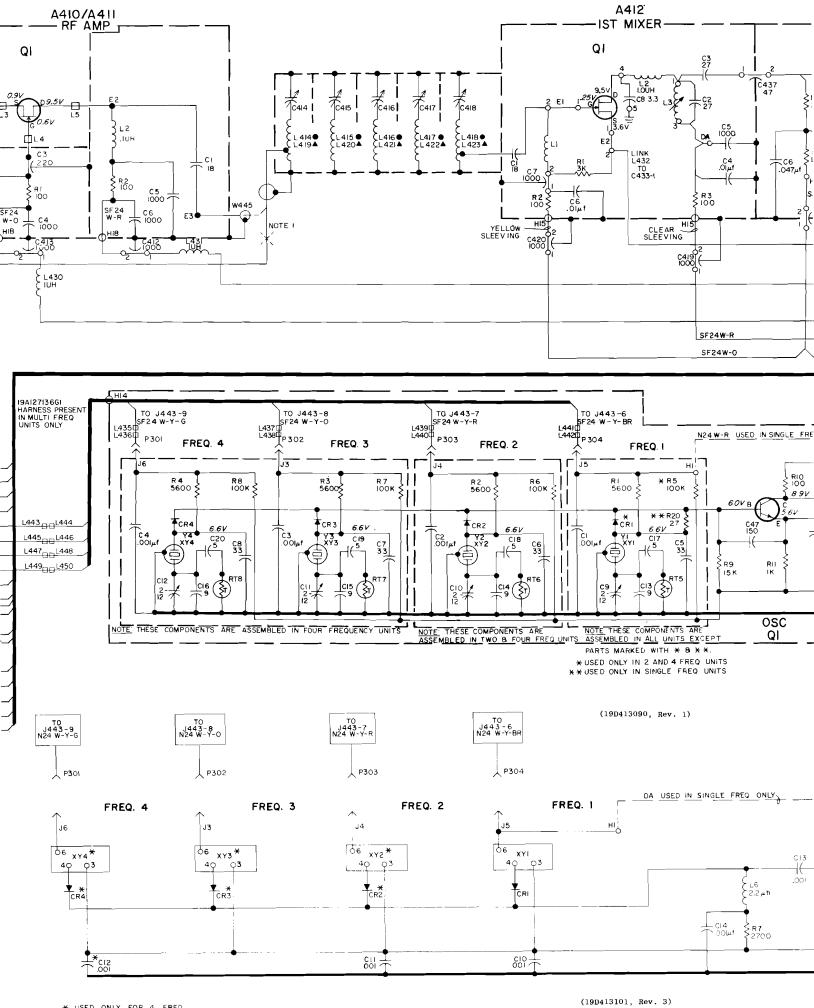
Issue 3











<sup>\*</sup> USED ONLY FOR 4 FREQ

<sup>450 - 470</sup> MHZ 406-420 MHZ

		т.			
MODELS WITH	MODELS		FREQ RANGE		U H.S RECFIVER
CIRCUIT	WITH ICOM	NO. OF	406-420-LO	CHANNEL	A410/A411
OSCILLATOR	OSCILLATOR	FREQS	450-470=HI	GUARD	PRESENT
4ER42EIO	4 ER 42GIO	1	LO		
4ER42E11	4ER42GII		HI		
4ER42E12		2	LO		
4ER42E13		2	H!		
4ER42EI4	4ER42GI4	4	LO		
4ER42E15	4 ER42G 15	4	HI		
4ER42E16	4ER42G16	1	LO		
4ER42E17	4ER42G17		HI	×	
4ER42E18		2	LO	×	
4ER42E19		2	H)	×	
4E R42E20	4ER42020	4	LO	×	•
4ER42E2I	4ER 42G 2I	4	HI	X	
4ER42E22	4ER42C22		LO		X
4ER42E23	4ER42G23		H1		. x
4ER42E24		2	LO		Х
4ER42E25		2	ні		Х
4ER42E26	4ER 42G26	4	LO		X
4ER42E27	4ER42G27	4	HI		X
4ER42E28	4ER42G28	_ i	LO	X	X
4ER 42E 2 9	4ER42G29		HI	X	X
4ER42E30		2	LO	×	×
4ER42E31		2	HI	X	Х
4ER42E32	4ER42G32	4	LO	X	X
4ER42E33	4ER42G33	4	HI	X	X

IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART

ALL RESISTORS ARE 1/2 WATT UNLESS OTH-FRWISE SPECIFIED AND RESISTOR VALLIES IN OHMS UNLESS FOLLOWED BY K=10.30 OHMS - NEG=1,000,000 OHMS - CAP-/CITOR VALUES IN PICOFARADS (EDUCADED BY UF= MICROFARADS, INDUCTANCE VALUES IN MICROFARAPS, UNLESS FOLLOWED BY UF= MICROFARAPS, UNDUCTANCE VALUES IN MICROFARRYS UNLESS FOLLOWED BY MH= MILLIHENRYS OR H=HENRYS.

#### VOLTAGE READINGS

VOLTAGE READINGS ARE TYPICAL READINGS MEASURED TO SYSTEM NEGATIVE (J442-8) WITH TEST SET MODEL 4EX3AIO OR A 20,000 OHM-PER-VOLT METER.

SEND SIGNAL IN WITH SQUELCH CONTROL FULLY COUNTERCLOCKWISE (MAXIUM SQUELCH)
US=SQUELCH CONTROL FULLY CLOCKWISE WITH A ONE MILLIVOLT MODULATED SIGNAL (UNSQUELCHED) AND 5 WATT AUDIO OUTPUT.

#### NOTE:

TO CHECK FOR PROPER OPERATION OF IST MIXER A412, MEASURE CURRENT IOV CIRCUIT (W-R LEAD), CURRENT WITH FIRST OSC XTAL REMOVED SHOULD BE 0.6 TO 0.8 MA. CURRENT WITH FIRST OSC OPERATING PROPERLY, SHOULD BE 1.2 TO 1.6 MA.

- ●THESE ARE ONLY PARTS PRESENT ON A429. ●LOW SPLIT 406-420 MHZ
- ▲HIGH SPLIT 450-470 MHZ
- \* LEADS TO BE TERMINATED AS SHORT AS POSSIBLE.
- VALUE OF A428-R47 IS DETERMINED BY SEST (SEE TEST SPEC 19A127182)

	REV
PL19E50088IGI	K
PL19E500881G2	L
PLI9E50088IG3	K
PL19E5008BIG4	L
PLI9B216119G3	
	Н
4EKI6AIO	Α
PLI9C311797G2	
	PLI9E50088IG2 PLI9E50088IG3 PLI9E50088IG4 PLI9B2I6119G3 PLI9D4I3I29G3

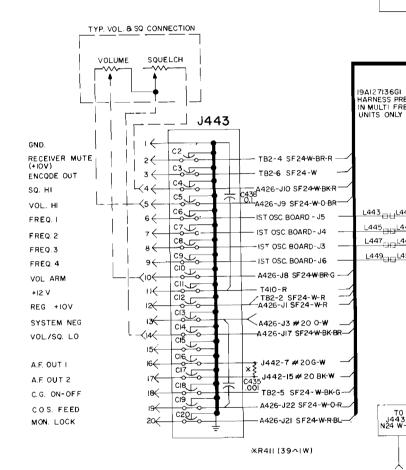
SYM		REV
NO	PARTS LIST	LETTER
A4 5	PLI9B2C44 9GI9	Δ
A416	P_I9B204419G20	
Д417	PLI9B204419G2	
4418	PL19B204419G22	Δ
Δ419	PEI9B2044I9G23	
A420	PL19B204419G24	

SYM NO	PARTS LIST	REV. LETTER
A432	PLi9C311726G1	Α
A433	PLI9C311726G2	Α
Δ434	PL19C3H726G3	Α
A435	PLI9C 311726G4	Α



H PRESENT ONLY IN NON-U.H.S. EIVER

C410 C 411 C2 18 410 **●** 412 **▲** L4(I ● L4(3▲ w444 NOTE : W441



QI

₫ 4

C 3

R I 100

C4 1000

L430 IUH

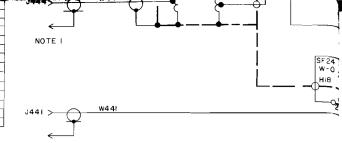
SF24 W-0

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0 - 33

ue 6

	4C K42C2U	4 E R420 20	4	LO	Х .	
	4ER42E2I	4ER 42G2I	4	н		
	4ER42E22	4ER42C22	1	LO		x
	4ER42E23	4ER42G23	1	HI	<del> </del>	
	4ER42E24		2	LO		<del></del>
	4ER42E25		2	HI		<del></del>
	4ER42E26	4ER42G26	4	10		·- ÷
	4ER42E27	4ER42G27	4	HI	<del></del>	Ŷ
	4ER42E28	4E R42G 2 8		10	x	·
	4ER 42E 2 9	4ER42G29		HI	×	<u>^</u>
	4ER42E30		2	LO	Ŷ	<u>x</u>
[	4ER42E31		2	HI	X	<u>x</u>
	4ER42E32	4ER42G32	4	LO	x	- x
(	4ER42E33	4ER42G33	4	HI	×	x



IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERV.CE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.

ALL RESISTORS ARE 1/2 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K=10,00 0,000 OHMS or MEG=1,000,000 OHMS or CAP+CITOR VALUES IN PROPERADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWED BY UF= MICROFARADS, INDUCTANCE VALUES IN MICROHENRYS UNLESS FOLLOWED BY MH= MILLHENRYS OR H= HEARRYS.

#### **VOLTAGE READINGS**

VOLTAGE READINGS ARE TYPICAL READINGS MEASURED TO SYSTEM NEGATIVE (J442-8)WITH TEST SET MODEL 4EX3AIO OR A 20,000 OHM-PER-VOLT METER.

S° NO SIGNAL IN WITH SQUELCH CONTROL FULLY COUNTERCLOCKWISE (MAXIUM SQUELCH) US° SQUELCH CONTROL FULLY CLOCKWISE WITH A ONE MILLIVOLT MODULATED SIGNAL (UNSQUELCHED) AND 5 WATT AUDIO OUTPUT.

#### NOTE:

TO CHECK FOR PROPER OPERATION OF IST MIXER A412, MEASURE CURRENT IOV CIRCUIT (W-R LEAD), CURRENT WITH FIRST OSC XTAL REMOVED SHOULD BE 0.6 TO 0.8 MA. CURRENT WITH FIRST OSC OPERATING PROPERLY, SHOULD BE 1.2 TO 1.6 MA.

- ■THESE ARE ONLY PARTS PRESENT ON A429.
- ●LOW SPLIT 406-420 MHZ
- ▲HIGH SPLIT 450-470 MHZ
- \* LEADS TO BE TERMINATED AS SHORT AS POSSIBLE.
- VALUE OF A42B-R47 IS DETERMINED BY SEST (SEE TEST SPEC 19A127182)

		REV
	PL19E50088IGI	K
	PL19E500881G2	نا
	PLI9E500881G3	К
	PLI9E 50088IG4	L
A424	PLI9B216119G3	
A426	PLI9D4I3I29G3	Н
A428	4EKI6AIÖ	Α
A429	PLI9C311797G2	L

SYM NO	PARTS LIST	RF/ LETTER
Ad 15	PL!9B2C44:9GI9	Α
A416	PLI9B2044 9G20	
Δ417	PLI9B204419G2i	
A418	PLI9B2044I9G22	Δ
4419	PLI9B2044I9G23	
4420	PL!9B2044I9G24	

#### **SCHEMATIC DIAGRAM**

406-470 MHz RECEIVER



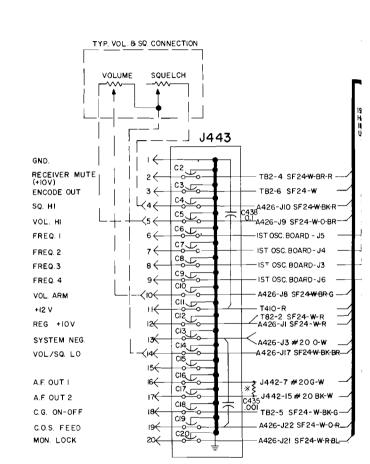
U.H.S. RECEIVER

RECEIVER.

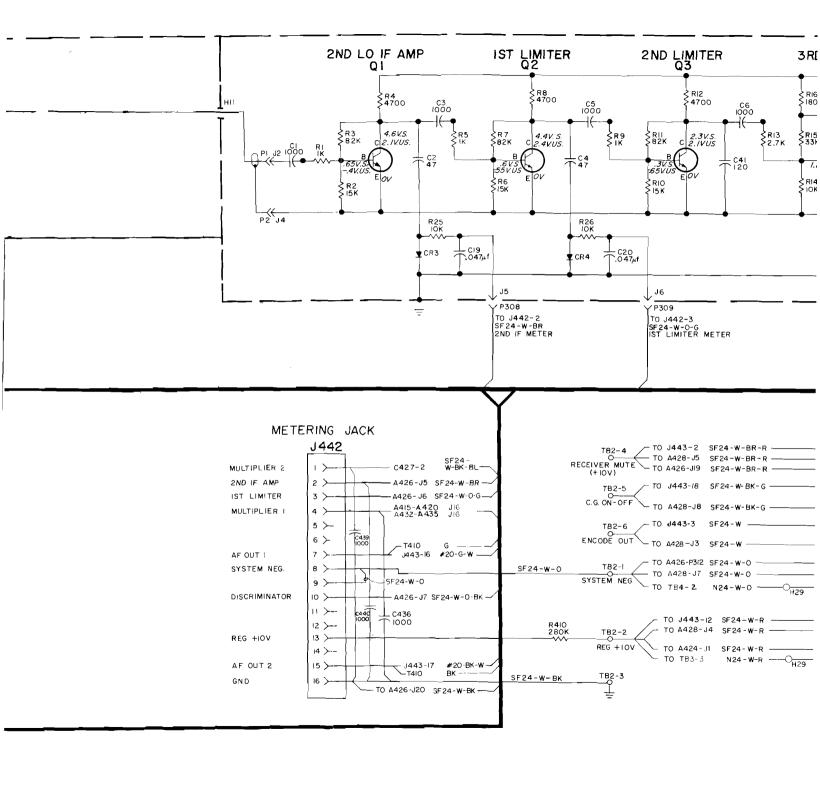
1. W444 AND W445 PRESENT ONLY IN

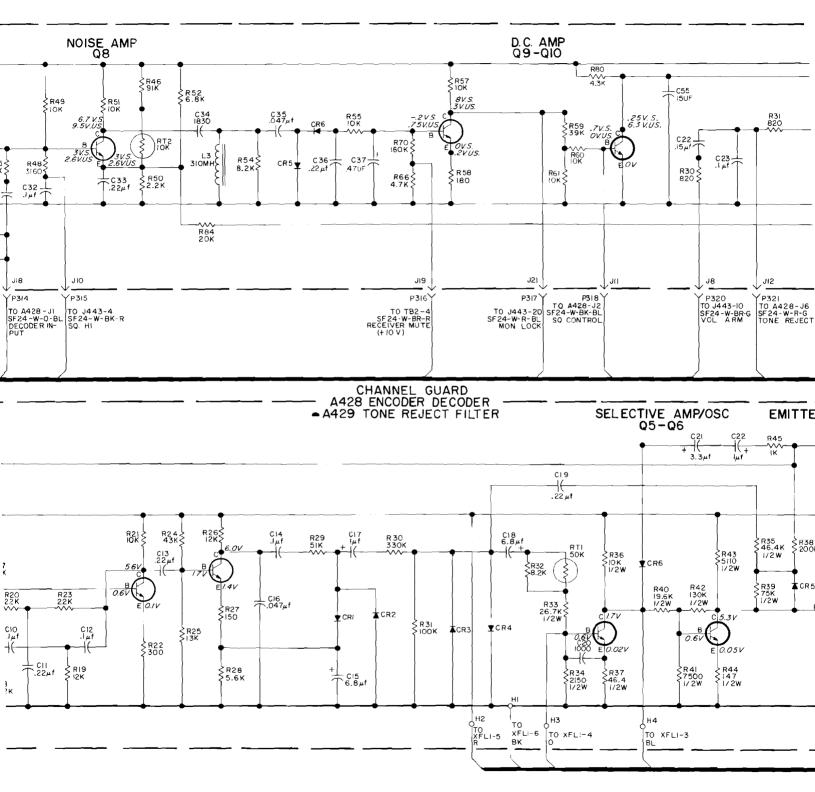
W441 PRESENT ONLY IN NON-U.H.S.

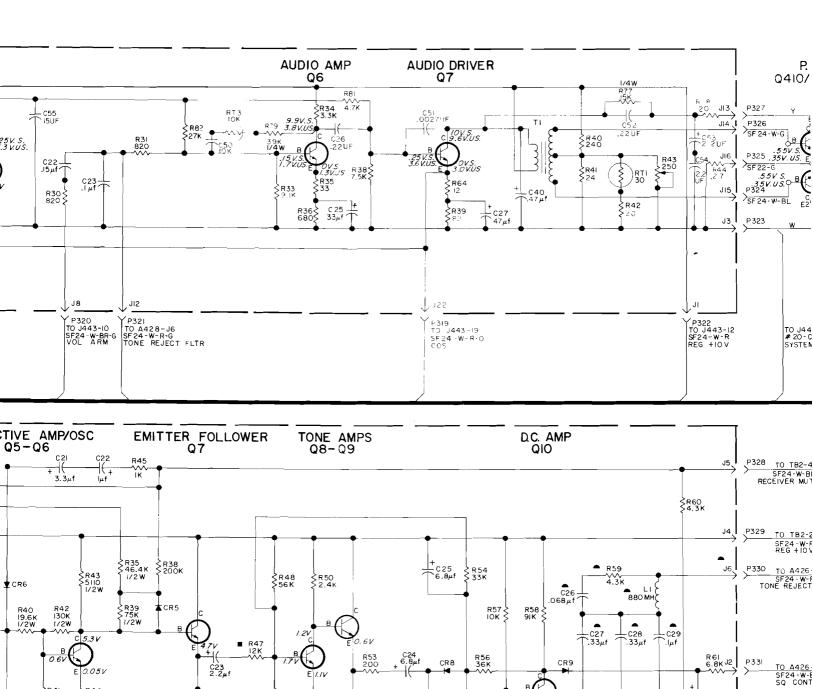
SYM REV.



※R4II (39~IW)







₹R55 ₹IOK

▼ CR7

⊂ C30 1.0μf

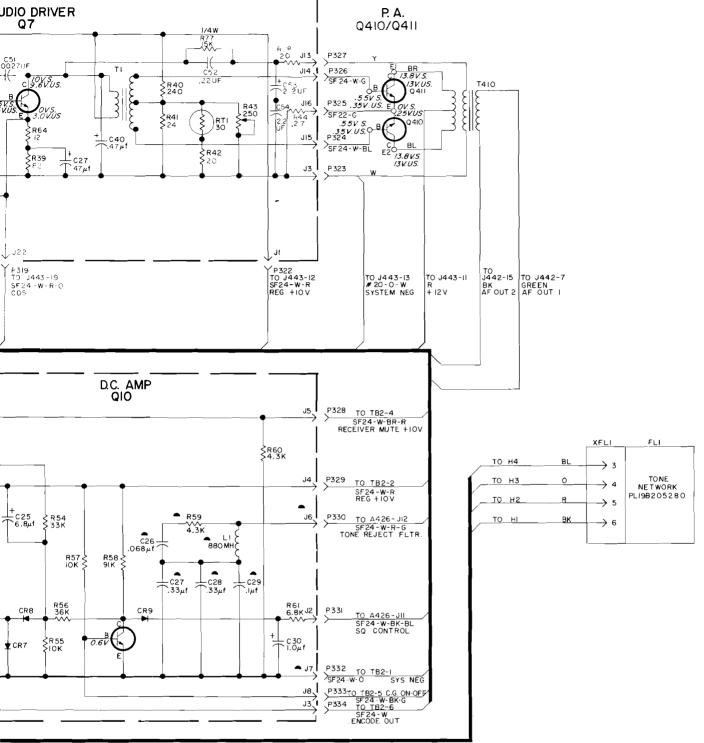
> P332 TO T82-I SF24-w-O S

J8 | P333<sub>TO</sub> TB2-5 C. | P334 TO TB2-6 C. | P334 TO TB2-6 C. | P34-W-E | P35-24-W-E | P35-24-W-E

ŠR49 ≶220K

₹R46

H4 TO XFLI-3 BL \$R51 \$330



#### **SCHEMATIC DIAGRAM**

406—470 MHZ RECEIVER MODELS 4ER42E10-33 & 4ER42G10-33

Issue 6

13

#### PARTS LIST

LBI-4021E

406-470 MHz RECEIVERS 4ER42E10-33, 4ER42G10-33

SYMBOL	GE PART NO.	DESCRIPTION
A410* and A411*		RF AMPLIFIER 19C317950G1
Cl and	5496218P245	
C2 C3	5493392P5	Ceramic, feed-thru: 220 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FA5C.
C4 thru	5493392P107	Ceramic, stand-off: .001 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type SSSA.
C6		
L1 and L2	19B209420P1	Coil, RF: 0.10 µh ±5%, 0.08 ohms DC res max; sim to Jeffers 4416-1J.
L3 thru L5	19A116632P1	Torridal core.
Q1	19A116154P1	N Change State Court
"	13811013471	N Channel, field effect.
Rl and R2	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
		In REV F and earlier:
A410* and A411*		RF AMPLIFIER A410 19C311975G1 (406-420 MHz) A411 19C311975G2 (450-470 MHz)
C1	5493392P107	
C2	7484398P3	sim to Allen-Bradley Type SSSA.  Silver mics: 250 pf +104 500 VDCW ctm +0
сз	5493392P7	Underwood Type JlHF.  Ceramic, feed-thru: .001 pf +100%-0% 500 yncw.
C4	5493392P107	Sim to Allen Bradley Type FA5C.  Ceramic, stand-off: .001 pf +100%-0% 500 ypcw-
C5	5496218P245	sim to Allen-Bradley Type SS5A.  Ceramic disc: 18 pf ±5%, 500 VDCW, temp
C6	5491601P124	coef -80 PPM.  Phenolic: 1.8 pf ±5%, 500 VDCW.
C7	7484389Pl	Variable 1.5-7 pf, temp coef 0 PPM; sim to Brie Style 503.
C8	5491601P122	Phenolic: 1.2 pf ±5%, 500 VDCw.
E1	19B209055P1	Terminal; sim to Electrical Industries ABAS-40W-RR.
L1	19B209420P1	Coil, RF: 0.10 µh ±5%, 0.08 ohms DC res max:
L2	19A127429P1	sim to Jeffers 4416-1J.  Coil.
L3	19A127429P1 19A127429P2	Coil.
Q1	19All6154Pl	N Channel, field effect.
}		

	GE PART NO.	DESCRIPTION	SYMBOL	GE PART N
		RESISTORS	C12	5494481P107
R1 and R2	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	and C13	5496218P548
R3	3R152P470K	Composition: 47 ohms ±10%, 1/4 w.	C15*	5494481P7
A412		FIRST MIXER ASSEMBLY 19C311974G1		
			Lı	
C1	5496218 <b>P3</b> 12	Coronic disc: 18 of +105 500 VDCW April	L2	
<b>01</b>	0430210F512	Ceramic disc: 18 pf ±10%, 500 VDCW, temp coef -150 PPM.	L3	19B209420P1
C2		(Part of L3).	L4	
C3	5496218P249	Ceramic disc: 27 pf ±5%, 500 VDCW, temp coef -80 PPM.	"	
C4	19B209243P1	Polyester: 0.01 µf ±20%, 50 VDCW.	Q1*	19A115329P1
C5	5493392P107	Ceramic, stand-off: .001 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type SS5A.		
C6	19B209243P1	Polyester: 0.01 µf ±20%, 50 VDCW.	1	19All6059Pl
C7	5493392P7	Ceramic, feed-thru: .001 pf +100%-0%, 500 VDCW; sim to Allen Bradley Type FA5C.	Q2	19A115991P1
C8		(Part of L3),	Rl	3R152P101K
			R2	3R152P181J
El	19B209055P8	Terminal, feed-thru.	R3	3R152P100K
and E2			R4	3R152P471K
		INDUCTORS	R5	3R152P680J
Ľ1	19A127430G1	Choke.	R6	3R152P273K
L2	10001644061	(Part of L3).	R7*	3R152P100K
L3 C2	19B216440G1 5496218P249	Coil assembly, includes: Ceramic disc: 27 pf ±5%, 500 VDCW, temp		
		coef -80 PPM,	T1 and T2	
C8*	19A116114P12	Ceramic: 3.3 pf ±5%, 100 VDCW; temp coef 0 PPM. Added to 19E500881G1, G3 by REV J, Added to 19E500881G2, G4 by REV K.	12	
L2	19B209420P113	Coil, RF: 1 µh ±10%, 0.74 ohms DC res max; sim to Jeffers 4426-6.	C2	5496218P350
	5491798P8	Tuning slug.	сз	5496218P248
		TRANSISTORS		
Q1	19A116154P1	N Channel, field effect,	L1	19 <b>B216373P</b> 5
		RESISTORS	L4	19B209420P1
R1	3R152P302J	Composition: 3000 ohms ±5%, 1/4 w.		F 403 George
R2 and R3	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	тз	5491798P7
ito			and T4	
A413 and		MULTIPLIER BOARD ASSEMBLY A413 19B216360G1		
A414		A414 19B216360G2	C5	5496218P439
C1	5494481P106	Ceramic disc: 330 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C6*	5496218P237
C2		(Part of T1).		
C3		(Part of T2).		5496218P436
C4 C5	5496372P149	Ceramic disc: 220 pf ±10%, 500 VDCW, temp coef -3300 PPM.		5496218P437
C6		(Part of T3). (Part of T4).		
C7		(Part of T3).	C7	5496218P750
C8		(Part of T4).	C8*	5496218P246
C9*	5494481P107	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Deleted by REV E.		
C10	5496372P149	Ceramic disc: 220 pf ±10%, 500 VDCW, temp coef -3300 PPM.		5496218P748
C11	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.		<b>549</b> 6218 <b>P</b> 749

<sup>\*</sup>COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

YMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
		RESISTORS			
R1	3R152P562J	Composition: 5600 ohms ±5%, 1/4 w.	Q1 *	19A115328P1	Silicon, NPN.
thru R4					
R5	3R152P104K	Composition: 0.1 megohm ±10%, 1/4 w.	] {		
thru R8			R1	3R152P301J	Composition: 300 ohms ±5%, 1/4 w.
R9	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.	R2	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
R10	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	R3	3R152P302J	Composition: 3000 ohms ±5%, 1/4 w.
R11	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.	R4	3R152P682J	Composition: 6800 ohms ±5%, 1/4 w.
and R12		·	R5	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
R13	3R152P151J	Composition: 150 ohms ±5%, 1/4 w.	R6	3R152P301J	Composition: 300 ohms ±5%, 1/4 w.
R14	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.			
R15	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	Tl	19B216372G1	Coil assembly. Includes tuning slug 5491798P7.
R17	3R152P103K	Composition: 10,000 ohms ±10%, 1/4 w.	ļí		
and R18			A422		CRYSTAL FILTER ASSEMBLY 19B204616G8
R20	3R152P270K	Composition: 27 ohms ±10%, 1/4 w.			13320101000
	JAZOZI ZIOK	composition. 21 ones itok, 1/4 w.			
			FL7	19C304358G1	Bandpass filter.
RT5 thru	19B209284P7	Disc: 62 ohms res nominal at 25°C, color code violet.	ł		RESISTORS
RT8		code viblet.	R10	3R152P512J	Composition: 5100 ohms ±5%, 1/4 w.
RT9	19B209284P8	Disc: 945 ohms res nominal at 25°C, color	811	3R152P332K	` '
		code gray.	"""	SKISZFSSZK	Composition: 3300 ohms ±10%, 1/4 w.
			A424		SECOND MIXER ASSEMBLY
т7		COIL ASSEMBLY		}	198216119G3
and T8		T7 19B204950G1 T8 19B204950G2			
			C2	19A116080P7	Polyester: 0.1 μf ±20%, 50 VDCW.
			СЗ	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to
C40	5496218P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef -80 PPM.	}	<b></b>	RMC Type JF Discap.
C41	5496218P251	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef	C7 and	19A116080P5	Polyester: 0.047 μf ±20%, 50 VDCW.
		-80 PPM.	C8 C9	5496219P369	
L5	19A121728P1			3490219P309	Ceramic disc: 180 pf ±5%, 500 VDCw, temp coef -150 PPM.
	19812172691	Coil. Includes tuning slug 5491798P5.	C10	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.
			C12	5496219 <b>P</b> 369	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef
XY1		Refer to Mechanical Parts (RC-1823).		E 400 01 0 = 401	-150 PPM.
thru XY4			C14	5496219P471	Ceramic disc: 220 pf ±5%, 500 VDCW, temp coef -220 PPM.
			C15	7491395P109	Ceramic disc: I000 pf ±10%, 500 VDCW; sim to
		When reordering give GE Part No. and specify		10411400000	RMC Type JL.
		exact freq needed.	C16	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.
		Crystal freq = (OF -12,4 MHz) - 24.	C17	19A116080P1	Polyester: 0.01 µf ±20%, 50 VDCW.
Y1	19 <b>8</b> 206576 <b>P</b> 6	Quartz: freq range 15175.000 to 17925.000 KHz,	C18	5490008P25	Silver mica: 82 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
thru Y4		temp range -30°C to +85°C. (405-420 MHz)	C19	5490008P19	Silver mica: 47 pf ±5%, 500 VDCW: sim to
Y1	19B206576P7	Quartz: freq range 17925.001 to 20685.000 KHz.			Electro Motive Type DM-15.
thru Y4	ļ	temp range -30°C to +85°C. (450-470 MHz)	C20	5490008P1	Silver mica: 5 pf ±0.5%, 500 VDCW; sim to Electro Motive Type DM-15.
			C23		(Part of T2).
421	ĺ	1F AMPLIFIER ASSEMBLY 19B216356G1	C24	5496219P43	Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef
			and C25	1	O PPM.
C1	19All6655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	J1	4033513P4	Contact, electrical; sim to Bead Chain L93-3.
C2*	7489162P21	Silver mica: 56 pf ±5%, 500 VDCW; sim to	1 1		
		Liectic motive Type Dm-15.	11		
		In 19E500881G1, G3 of REV H and earlier: In 19E500881G2, G4 of REV J and earlier:	L1 thru	19C311181G3	Coil assembly,
	5490008P21	Silver mica: 56 pf ±5%, 500 VDCW; sim to	L3		
СЗ	5496218P650	Electro Motive Type DM-15.		400004555	
(3	5496218P650	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -470 PPM.	P1	4029840P2	Contact, electrical: sim to Amp 42827-2.
C4	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to	P2	4029840Pl	Contact, electrical: sim to Amp 41854.
	_	RMC Type JF Discap.		1	
C5 and C6	19B209243P5	Polyester: 0.047 μf ±20%, 50 VDCW.			
1					
			( I	i .	I .
				]	

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL
			C19 and	19A116080P5	Polyester: 0.047 μf ±20%, 50 VDCW.	C52*
Q2	19A115245P1	Silicon, NPN.	C20			
Q3	19A115123P1	Silicon, NPN; sim to Type 2N2712.	C21*	19A116080P3	Polyester: 0.022 μf ±20%, 50 VDCW.	C53*
Q4	19A115245P1	Silicon, NPN.			Earlier than REV A:	C54*
		RESISTORS		19B209243P1	Polyester: 0.01 µf ±20%, 50 VDCW.	C55
R1	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.	C22	19A116080P108	Polyester: 0.15 µf ±10%, 50 VDCW.	
and R2	Ì		C23	19Al16080P107	Polyester: 0.1 μf ±10%, 50 VDCW.	CR1
R3	3R77P512J	Composition: 5100 ohms ±5%, 1/2 w.	C24*	19B209243P106	Polyester: 0.068 μf ±10%, 50 VDCW. Deleted by REV A.	and CR2
R4	3R152P333K	Composition: 33,000 ohms ±10%, 1/4 w.	C25	5496267P6	Tantalum: 33 µf ±20%, 10 VDCW; sim to Sprague	CR3
R5	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	200		Type 150D,	and CR4
R6	3R77P332K	Composition: 3300 ohms ±10%, 1/2 w.	C26*	19A116080P109	Polyester: 0.22 µf ±10%, 50 VDCW.	] }
R7	3R77P123K	Composition: 12,000 ohms ±10%, 1/2 w.			In REV E and earlier:	
R8	3R77P622J	Composition: 6200 ohms ±5%, 1/2 w.		5496267P28	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Sprague Type 150D.	CRS
R9	3R77P302J	Composition: 3000 ohms ±5%, 1/2 w.			Earlier than REV A:	CR
R10	3R77P202J	Composition: 2000 ohms ±5%, 1/2 w.		19B209243P14	Polyester: 0.33 μf ±20%, 250 VDCW.	CR
R11	3R77P201J	Composition: 200 ohms ±5%, 1/2 w.	C27*	5496267P2	Tantalum: 47 μf ±20%, 6 VDCW; sim to Sprague	CR
	ļ				Type 150D.	
Т2	ļ	COIL ASSEMBLY		549626756	Earlier than REV C:	J1
		I9B216120G2		5496267 <b>P</b> 6	Tantalum: 33 μf ±20%, 10 VDCW; sim to Sprague Type 150D.	th J2
			C28*	5496267P229	Tantalum: 0.68 µf ±10%, 35 YDCW; sim to Sprague Type 150D. Deleted by REV A.	
C23	5496218P258	Ceramic disc: 62 pf ±5%, 500 VDCW, temp coef -80 PPM.	C29*	5496267P17	Tantalum: 1.0 µf ±10%, 35 VDCW; sim to Sprague Type 150D. Deleted by REV A.	L1
	5491798P3	Tuning slug.	c30	19A116080P8	Polyester: 0.15 µf ±20%, 50 VDCW.	L2
			C31	19A116080P102	Polyester: 0.015 µf ±10%, 50 VDCW.	L3
¥2	19A110398P1	Quartz: freq 11945.00 KHz, temp range -30°C	C32	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.	"
		to +75°C.	C33	19A116080P9	Polyester: 0.22 µf ±20%, 50 VDCW.	Q1
26		IF AUDIO AND SQUELCH BOARD	C34	4029003P207	Silver mica: 1830 pf ±2%, 500 VDCW; sim to	th Q6
		19D413129G3	C35	104116080DE	Electro Motive Type DM-20.	Q7
			C35	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.	Q8
Cl	5494481P111	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to	C36+	19A116080P9	Polyester: 0.22 µf ±20%, 50 VDCW.	ep qe
		RMC Type JF Discap.		19B209243P7	Earlier than REV C:	Q1
C2	5496219P717	Ceramic disc: 47 pf ±10%, 500 VDCW, temp coef -750 PPM.	C37*	5496267P28	Polyester: 0.1 \( \mu f \pm 20\%, 50 \) VDCW.  Tantalum: 0.47 \( \mu f \pm 20\%, 35 \) VDCW; sim to	11
С3	5494481P111	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.		J430207F20	Sprague Type 150D.  Earlier than REV A:	
C4	5496219P717	Ceramic disc: 47 pf ±10%, 500 VDCW, temp coef -750 PPM.		5496267P17	Tantalum: 1.0 uf ±20%, 35 VDCW; sim to	<b>!</b> [
C5 and	5494481P111	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C38*	5496267P10	Sprague Type 150D.  Tantalum: 22 \( \mu \frac{1}{2} \text{ \frac{1}{2}}  \frac{1	R1
C6		-			Sprague Type 150D. Deleted by REV C.  Earlier than REV A:	R3
C7 C8	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.		5496267P14	Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague	R4
	19A116656P180J1	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.			Type 150D.	R5
C9 and	5490008P37	Silver mica: 270 pf ±5%, 500 VDCW; sim to	C39	19A116080P1	Polyester: 0.01 μf ±20%, 50 VDCW.	R6
C10		Electro Motive Type DM-15.	C40*	5496267P28	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Sprague Type 150D.	R7
C11	5496219P656	Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef -470 PPM.			Earlier than REV A:	RE
C12	5494481P108			19B209243Pl17	Polyester: 0.22 µf ±10%, 50 VDCW.	RS RS
	2 YO T KOT FIND	Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C41	5490008P129	· ·	RJ
C13	19All5680Pl07	Electrolytic: 100 µf +150% -10%, 15 VDCW; sim to Mallory Type TT.			Silver mica: 120 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.	RI
C14	19A115680P104	Electrolytic: 50 \( \mu f +150\% -10\% \), 25 \( \mathrm{VDCW} \); sim	C42*	19B209243P4	Polyester: 0.033 µf ±20%, 50 VDCW. Deleted by REV A.	R3
and C15		to Mallory Type TT.	C43 *	5496267P213	Tantalum: 2.2 µf ±10%, 20 VDCW; sim to Sprague	R1
016	5494481p112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to	C49*	5496267P9	Type 150D. Deleted by REV A.	R1
C17	19A116080P7	RMC Type JF Discap.			Tantalum: 3.3 µf ±20%, 15 VDCW; sim to Sprague Type 150D. Added by REV A. Deleted by REV C.	R1
C18	5494481P108	Polyester: 0.1 µf ±20%, 50 VDCW.	C50*	19A116080P7	Polyester: 0.1 μf ±20%, 50 VDCW. Added by REV A.	R1
C18	944491b108	Ceramic disc: 470 pf $\pm 10\%$ , 1000 VDCW; sim to RMC Type JF Discap.	C51*	5494481P127	Ceramic disc: 2700 pf ±20%, 1000 VDCW; sim to	RI
	ľ				RMC Type JF Discap. Added by REV A.	RI
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- 1			1		1	R2

SYMBO	L GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
C19 and C20	19A116080P5	Polyester: 0,047 μf ±20%, 50 VDCW.	C52*	19Al16080P109	Polyester: 0.22 $\mu f$ $\pm 10\%$ , 50 VDCW. Added by REV A.
C21 4	19A116080P3	Polyester: 0.022 µf ±20%, 50 YDCW. Earlier than REV A:	C53* and C54*	5496267P213	Tantalum: 2,2 µf ±10%, 20 VDCW; sim to Sprague Type 150D, Added by REV A.
	19B209243P1	Polyester: 0.01 $\mu$ f $\pm$ 20%, 50 VDCW.	C55*	5496267P14	Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D. Added by REV C.
C22	19A116080P108	Polyester: 0.15 µf ±10%, 50 VDCW.			
C23	19A116080P107 19B209243P106	Polyester: 0.1 µf ±10%, 50 VDCW.  Polyester: 0.068 µf ±10%, 50 VDCW. Deleted	CR1 and	19A115250P1	DIODES AND RECTIFIERS Silicon,
C25	5496267P6	by REV A.  Tantalum: 33 µf ±20%, 10 VDCW; sim to Sprague Type 1500.	CR2 CR3*	19A115250P1	Silicon.
C26 *	19A116080P109	Polyester: 0.22 µf ±10%, 50 VDCW.	and CR4+		In REV F and earlier:
		In REV E and earlier:		4038056P1	Germanium.
	5496267P28	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Sprague Type 150D.	CR5 and CR6	19A115250P1	Silicon.
		Earlier than REV A:	CR7+	19A115250P1	Silicon, Deleted by REV C.
C27+	19B209243P14 5496267P2	Polyester: 0.33 µf ±20%, 250 VDCW.  Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague	CR8*	19A115250P1	Silicon. Added by REV A. Deleted by REV C.
		Type 150D.			Jacks and receptacles
	5496267 <b>P</b> 6	Earlier than REV C: Tantalum: 33 µf ±20%, 10 VDCW; sim to Sprague Type 150D.	J1 thru	4033513P4	Contact, electrical; sim to Bead Chain L93-3.
C28*	5496267P229	Tantalum: 0.68 µf ±10%, 35 YDCW; sim to Sprague Type 150D. Deleted by REV A.	J22		
C29 *	5496267P17	Tantalum: 1.0 µf ±10%, 35 VDCW; sim to Sprague Type 150D. Deleted by REV A.	L1	19A115711P6	Transformer, freq: 455 KHz; sim to TOKO PEFCN-14733-CX12.
C30	19A116080P8	Polyester: 0.15 μf ±20%, 50 VDCW.	L2	19A115711P7	Transformer, freq: 455 KHz; sim to TOKO PEFCN-14734-ENL2.
C31	19A116080P102	Polyester: 0.015 μf ±10%, 50 VDCW.	L3	19A127134G1	Choke.
C32	19A116080P7	Polyester: 0.1 μf ±20%, 50 VDCW.			
C33	19A116080P9 4029003P207	Polyester: 0.22 µf ±20%, 50 VDCW.	Q1 thru	19A115123P1	Silicon, NPN; sim to Type 2N2712.
034	4029003P207	Silver mica: 1830 pf ±2%, 500 VDCW; sim to Electro Motive Type DM-20.	Q6		
C35	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.	Q7	19A115300P4	Silicon, NPN; sim to Type 2N3053,
C36+	19A116080P9	Polyester: 0.22 μf ±20%, 50 VDCW.	Q8	19A115123P1	Silicon, NPN; sim to Type 2N2712.
		Earlier than REV C:	Q9 Q10+	19A115362P1 19A116774P1	Silicon, NPN; sim to Type 2N2925.
C37*	19B209243P7 5496267P28	Polyester: 0.1 µf ±20%, 50 VDCW.	4101	19/110/1491	Silicon, NPN; sim to Type 2N5210.  In REV G and earlier:
Care	5496267928	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Sprague Type 150D.  Earlier than REV A:		19A115123P1	Silicon, NPN; sim to Type 2N2712.
	5496267P17	Tantalum: 1.0 µf ±20%, 35 VDCW; sim to			
C38*	5496267P10	Sprague Type 150D.	R1	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.
"	5490207910	Tantalum: 22 $\mu$ f $\pm$ 20%, 15 VDCW; sim to Sprague Type 150D. Deleted by REV C.	R2	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.
		Earlier than REV A:	R3	3R77P823K	Composition: 82,000 ohms ±10%, 1/2 w.
	5496267P14	Tantalum: 15 μf ±20%, 20 VDCW; sim to Sprague Type 150D.	R4	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.
C39	19A116080P1	Polyester: 0.01 µf ±20%, 50 VDCW.	R5	3R77P102K 3R77P153J	Composition: 1000 ohms ±10%, 1/2 w.
C40+	5496267P28	Tantalum: 0.47 μf ±20%, 35 YDCW; sim to	R7	3R77P1533 3R77P823K	Composition: 15,000 ohms ±5%, 1/2 w.  Composition: 82,000 ohms ±10%, 1/2 w.
		Sprague Type 150D.	R8	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.
	19B209243P117	Earlier than REV A: Polyester: 0.22 \( \mu \frac{1}{2} \text{ \psi} \text{ \psi} \text{ 10\%, 50 VDCW.} \)	R9	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.
C41	5490008P129	Silver mica: 120 pf ±10%, 500 VDCW; sim to	R10	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.
}		Electro Motive Type DM-15.	R11	3R77P823K	Composition: 82,000 ohms ±10%, 1/2 w.
C42*	19B209243P4	Polyester: 0.033 µf ±20%, 50 VDCW. Deleted by REV A.	R12	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.
C43+	5496267P213	Tantalum: 2.2 µf ±10%, 20 VDCW; sim to Sprague Type 150D. Deleted by REV A.	R13	3R77P272K	Composition: 2700 ohms ±10%, 1/2 w.
C49+	5496267P9	Tantalum: 3.3 µf ±20%, 15 VDCW; sim to Sprague	R14 R15	3R77P103J 3R77P333J	Composition: 10,000 ohms ±5%, 1/2 w.  Composition: 33,000 ohms ±5%, 1/2 w.
C50+	19A116080P7	Type 150D. Added by RÉV A. Deleted by RÉV C. Polyester: 0.1 µf ±20%, 50 VDCW. Added by	R16	3R77P181K	Composition: 180 ohms ±10%, 1/2 w.
ł		REV A.	R17	3R152P471J	Composition: 470 ohms ±5%, 1/4 w.
C51*	5494481P127	Ceramic disc: 2700 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Added by REV A.	R18 and R19	3R152P513J	Composition: 51,000 ohms ±5%, 1/4 w.
			R20	3R152P472K	Composition: 4700 ohms ±10%, 1/4 w.
			R21 and R22	3R77P362J	Composition: 3600 ohms ±5%, 1 2 w.
			RZZ		

<b>0</b> S	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
, 1 , d'	L426	19B204938G20	Coil.			MECHANICAL PARTS (SEE RC-1823)
0	L427	19B204936P16	Coil.			(BE RC-1823)
	L428 and L429	7488079P18	Choke, RF: 15 µh ±10%, 1.2 ohms DC res; sim to Jeffers 4421-9K.	1	19C303495G4 19C303385G1	Bottom cover. (Station)  Bottom cover. (Mobile)
	L430 and	7488079P6	Choke, RF: 1.0 $\mu h$ ±10%, 0.30 ohms DC res; sim to Jeffers 4411-8K.	2	19C317344P3	Heat sink.
1	L431			3	19A121723P1	Support. (Mounts C425 and C426)
	L432	19A127433P1	Coil.	4	4033089P1	Clip. (Part of XY1-XY4).
3	L433 and	19A115700P2	Bead, ferrite.	5	19B200525P9	Rivet. (Part of XY1-XY4).
7	L434			6	19A115793P1	Contact. (Part of XY1-XY4).
3	P305	4029840P2	Contact, electrical: sim to Amp 42827-2.	7	4039307P1	Crystal socket. (Part of XY1-XY4).
	thru P322	102301012	ospitate, electronic state to himp 1252. 5.	8	4035306P59	Fiber washer, (Used with Y2),
lo o	P323	4029840P1	Contact, electrical: sim to Amp 41854.	9	4034252P5	Can. (Used with T1).
11	P324	4029840P2	Contact, electrical: sim to Amp 42827-2.	10	19C303389G1	Chassis.
12	P325	4029840P1	Contact, electrical: sim to Amp 41854.	11	19A121722P1	Plate,
13	P326	4029840P2	Contact, electrical: sim to Amp 42827-2.	12	4036765G4	Screw. (Part of C410, C411, C414-C418, C423 and C424).
14	P3 27	4029840P1	Contact, electrical: sim to Amp 41854.	13	7117825P1	Washer. (Part of C410, C411, C414-C418, C423
15	P328	4029840P2	Contact, electrical: sim to Amp 42827-2.	1,4	10413173451	and C424). Support (Mounts C419 and C420)
16	thru P335			14 15	19A121724P1 19A127372P1	Support. (Mounts C419 and C420).  Support. (Mounts C427, C430 and C431).
17	P410	4029840P2	Contact, electrical: sim to Amp 42827-2.	16	7145451Pl	(Not Used).
.18	and P411			17	19B204583G3	Hinge.
19			~ ~ TRANS1STORS	18	19B216727P1	Support. (Used with Q410 and Q411),
20	Q410*	19A116741P1	Silicon, NPN.	19	19A116023P2	Plate, insulated, (Used with Q410 and Q411).
21	and Q411*		ln 19E500881Gl, G3 of REV B-K:	20	19A115222P3	Insulator, (Used with Q410 and Q411).
.22			In 19E500881G2, G4 of REV B-L:	21	4029851P6	Clip, loop.
23		19A116203P2	Silicon, NPN.	22	19B204583G1	Hinge.
24			Earlier than REV B:	23	19B204583G2	Hinge.
.25	ì	19A115948P1	Silicon, NPN.	24	19A121676P1	Guide pin.
<b>26</b>	I		RESISTORS	25	19C303495G3	Top cover. (Station, except Repeaters and VM).
127	R410	19A116278P444	Metal film: 0.28 megohm ±2%, 1/2 w.		19C303676G2	Top cover. (Station, Repeater and VM only).
128	R411*	3R78P390K	Composition: 39 ohms ±10%, 1 w. Added by		19C303385G2	Top cover, (Mobile).
129			REV B.	26	19A121297P2	Angle.
13C 131			~ ~ TRANSFORMERS	27	7160861P4	Nut, sheet spring. (Used to secure cover).
131	T410	19A116041P1	Audio freq: freq range 300 to 4000 Hz	28	4036555P1	Insulator, disc. (Used with Q7 on A426).
133			Pri: 1.00 ohm ±15% DC res, Sec 1: 0.23 ohm ±10% DC res, Sec 2: 10.5 ohms ±15% DC res.	29	4035267P2	Button, plug.
134			Sec 2. 10.3 Onias 113% AC Pes.	30	N115P1508C13	Screw, flathead, self tap: No. 8 x 30.
135	1		TERMINAL BOARDS			
136	TB1	7487424P2	Miniature, phen: l terminal.			
137	TB2	7487424P26	Miniature, phen: 6 terminals.		1	
138	TB3 and	7487424P24	Minlature, phen: 3 terminals.			
138	TB4					
140						
<b>14</b> I	W441	19B205634G3	Coaxial cable: 50 ohm, approx 5 inches long, Includes (J441) 19B209122P3 connector.			
142	W444	19B205634G7	Coaxiai cable: 50 ohm, approx 7 inches long.			
R4:	W445	19A122550G1	Includes (J444) 198209122P4 connector.			
R44	"110	19812233001	RF: 50 ohm imp, approx 4 inches long.		}	
R45 RDC R46			MULTI-FREQUENCY MODIFICATION KIT 19A127096G1 and G2			
		19A127136G1	Harness assembly,			
	P301 thru P304	4029840P2	Contact, electrical; sim to Amp 42827-2. (Part of 194127136Gl Harness assembly).			
847 847	L435 thru L442	19A115700P2	Bead, ferrite. (Part of 19A127136G1 Harness assembly).			
	L443 thru L450	19A115700P2	Bead, ferrite.			
			1	- 1	1	1

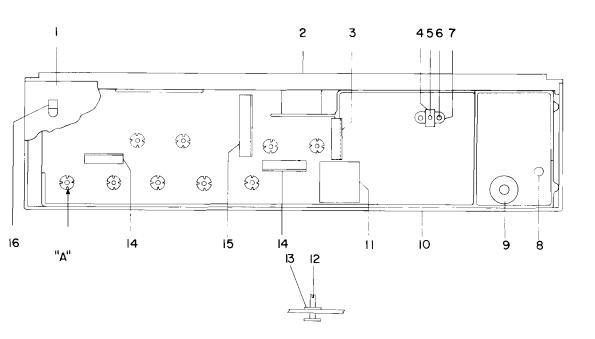
DN	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
±5%, 1/4 w.	C4	5491601P123	Phenolic: 1.5 pf ±5%, 500 VDCW; sim to Quality			CHASSIS AND RF CIRCUIT
±5%, 1/4 w.	C5	E4044017110	Components Type MC.			19E500881Gl thru G4
5%, 1/4 w.	(3)	5494481P112	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.			
5%, 1/4 w.	C6		(Part of T1),	C410 and		Refer to Mechanical Parts (RC-1823),
5%, 1/4 w.	C7		(Part of T2).	C411		
, 1/4 w. 5%, 1/4 w.	C8	5496219P238	Ceramic disc: 7 pf ±5%, 500 VDCW; temp coef -80 PPM.	C412 and C413	5493392P7	Ceramic, feed-thru: .001 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type FA5C.
±5%, 1/4 w.	C9	5490008P135	Silver mica: 220 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.	C414 thru		Refer to Mechanical Parts (RC-1823).
, 1/4 w. 1/4 w.	C10 thru C14	5494481P112	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C418 C419 thru	5493392P7	Ceramic, feed-thru: .001 pf +100%-0%, 500 VDCW;
, 1/4 w.			Dlodes and rectifiers	C422		sim to Allen-Bradley Type FASC.
1/4 w. 5%, 1/4 w.	CR1 thru CR5	19 <b>A1</b> 15250P1	Silicon.	C423 and C424		Refer to Mechanical Parts (RC-1598).
5%, 1/4 w.	CAS		JACKS AND RECEPTACLES	C425	5493392P7	Ceramic, feed-thru: .001 pf +100%-0%, 500 VDCW;
5%, 1/4 w.	J1 thru	4033513 <b>P</b> 4	Contact, electrical: sim to Bead Chain L93-3.	thru C427		sim to Allen-Bradley Type FA5C.
10%, 1/4 w. 5%, 1/4 w.	J6 J15	4033513P4		C428	5496267P11	Tantalum: 68 µf ±20%, 15 VDCW; sim to Sprague Type 150D.
, 1/4 w.	and J16	403331324	Contact, electrical: sim to Bead Chain L93-3.	C429	19A115680P4	Electrolytic: 50 µf +150% -10%, 25 VDCW; sim to Mallory Type TT.
, 1/4 w.				C430 and C431	5493392P7	Ceramic, feed-thru: .001 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type FA5C.
5, 1/4 w.	L1 and L2	7488079P16	Choke, RF: 10 µh ±10%, 0.6 chm DC res max; sim to Jeffers 4421-7K.	C433	5493392P107	Ceramic, stand-off: .001 pf +100%-0%, 500 VDCW;
%, 1/4 w.	L5		(Part of Tl or T2).	C435	7774750P4	sim to Allen-Bradley Type SS5A.  Ceramic disc: .001 µf +100% -0%, 500 VDCW.
RS	L6	7488079P35	Choke, RF: 2.20 µh ±10%, 0.50 ohms DC res max; sim to Jeffers 4412-9K.	and C436		
0%, color code 763H.			TRANSISTORS	C437	5493392P3	Ceramic, feed-thru: 47 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FASC.
	Q1	19A115330P1	Silicon, NPN.	C438 C439*	5491189P6	Polyester: 0.1 µf ±20%, 50 VDCW.
pins rated at 1 amp es of cable.			RESISTORS	and C440*	5494481Pl1	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Added by REV A.
ILTER	R1	3R152P102J	Composition: 1000 chms ±5%, 1/4 w.	C441*	5493392P7	Ceramic, feed-thru: .001 pf +100%-0%, 500 VDCW;
2	R2	3R152P151J	Composition: 150 ohms ±5%, 1/4 w.			sim to Allen-Bradley Type FA5C. Added by REV F.
	R3	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	1		DIODES AND RECTIFIERS
S	R4 R5	3R152P101K 3R152P103K	Composition: 100 ohms ±10%, 1/4 w.  Composition: 10,000 ohms ±10%, 1/4 w.	CR1*	19A116062P2	Selenium. Deleted in 19E500881G1, G3 by REV H, Deleted in 19E500881G2, G4 by REV J.
0 VDCW.	and R6		, , , , , , , , , , , , , , , , , , , ,		ı	JACKS AND RECEPTACLES
	R7	3R77P272K	Composition: 2700 ohms ±10%, 1/2 w.	J44I		(Part of W441).
O VDCW.				J442	19B205689G2	Connector: 18 contacts rated at 5 amps min at 1000 VDC max,
EPTACLES	T1 and		COIL ASSEMBLY T1 19B204950G1	J443	19C3O3426G1	Connector: 20 pin contacts.
Bead Chain L93-3.	T2		T2 19B204950G2	J444		(Part of W444).
to Artted AC5672.	C6	5496218P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef -80 PPM.	L410	19B204938G7	Coil,
to Mitted Accora.	C7	5496218P251	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef	L411	19B204938G15	Coil.
RS			-80 РРМ.	L412	19B204938G8	Coil.
, 1/4 w.		1	INDUCTORS	L413	19B204938G16	Coil.
	L5	19A121728P1	Coil. Includes tuning slug 5491798P7.	L414	19B204938G11	Co11.
, 1/4 w.			OSCILLATORS	L415 thru L417	19B204936P13	Coil.
LIER BOARD 1726G1			When reordering specify ICOM Frequency. ICOM Freq = Operating Freq -12.4 MHz ÷ 24.	L418	19B204938G17	Coil.
1726G2 1726G3	Yl	4EG26A10	Integrated Circuit Oscillator Module (ICOM).	L419	19B204938G12	Coil.
1726G4	thru Y4	INGLORIO	integrated circuit Oscillator module (ICOM).	L420 thru	19B204936P14	Coil.
s		19D413070P1	Cap, decorative.	L422		
, 1000 VDCW; sim				L423	19B204938G18	Coil.
	XY1 thru XY4	19B216043G1	Socket, (ICOM).	L424 L425	19B204938G19 19B204936P15	Coil. Coil.
				1		

	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
w	Q9	19A115123P1	Silicon, NPN; sim to Type 2N2712.	R47C	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.
cw.	and Q10			R47D	3R152P113J	Composition: 11,000 ohms ±5%, 1/4 w.
				R47E	3R152P123J	Composition: 12,000 ohms ±5%, 1/4 w.
CW.	R1	3R152P682K	Composition: 6800 ohms ±10%, 1/4 w.	R47F	3R152P133J	Composition: 13,000 ohms ±5%, 1/4 w.
CW.	R2	3R152P683J	Composition: 68,000 ohms ±5%, 1/4 w.	R47G	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.
	R3	3R152P822J	Composition: 8200 ohms ±5%, 1/4 w.	R47H	3R152P752J	Composition: 7500 ohms ±5%, 1/4 w.
cw.	R4	3R152P152J	Composition: 1500 ohms ±5%, 1/4 w.	R48	3R152P563J	Composition: 56,000 ohms ±5%, 1/4 w.
,	R5	3R152P682K	Composition: 6800 ohms ±10%, 1/4 w.	R49	3r152P224J	Composition: 0.22 megohms ±5%, 1/4 w.
w.	R6	3E152P201J	Composition: 200 ohms ±5%, 1/4 w.	R50	3R152P242J	Composition: 2400 ohms ±5%, 1/4 w.
<u>.</u>	R7	3R152P113J	Composition: 11,000 ohms ±5%, 1/4 w.	R51	3R152P331J	Composition: 330 ohms ±5%, 1/4 w.
sim to	R8	3R152P562J	Composition: 5600 ohms ±5%, 1/4 w.	R52	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.
im to	R9	3R152P313J		R53	3R152P201J	Composition: 200 ohms ±5%, 1/4 w.
w.		l	Composition: 11,000 ohms ±5%, 1/4 w.	R54	3R152P333J	Composition: 33,000 ohms ±5%, 1/4 w.
im to	R10	3R152P512J	Composition: 5100 ohms ±5%, 1/4 w.	R55	3R152P103J	· · · · · · · · · · · · · · · · · · ·
	R11	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.			Composition: 10,000 ohms ±5%, 1/4 w.
im to	R12	3R152P822J	Composition: 8200 ohms ±5%, 1/4 w.	R56	3R152P363J	Composition: 36,000 ohms ±5%, 1/4 w.
w	R13	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.	R57	3R152P103K	Composition: 10,000 ohms ±10%, 1/4 w.
VDCW; sim to	R14	3R152P133J	Composition: 13,000 ohms ±5%, 1/4 w.	R58	3R152P913J	Composition: 91,000 ohms ±5%, 1/4 w.
VLCW; Sim to	R15	3R152P510J	Composition: 51 ohms ±5%, 1/4 w.	R59*	3R152P182J	Composition: 1800 ohms ±5%, 1/4 w.
sim to	R16	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.			In REV C and earlier:
	R17	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.		3R152P432J	Composition: 4300 ohms ±5%, 1/4 w.
in to	R18	3R152P622J	Composition: 6200 ohms ±5%, 1/4 w.	R60	3R152P432J	Composition: 4300 ohms ±5%, 1/4 w.
sim to	R19	3R152P123J	Composition: 12,000 ohms ±5%, 1/4 w.	R61	3R152P682K	Composition: 6800 ohms ±10%, 1/4 w.
[	R20	3R152P223J	Composition: 22,000 ohms ±5%, 1/4 w.			
in to	R21	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	1 ]		
1m to	R22	3R152P301J	Composition: 300 ohms ±5%, 1/4 w.	RT1	5490828P22	Thermistor: 50,000 ohms ±10%, color code yellow; sim to Globar Type 763H.
1m (0	R23	3R152P223J	Composition: 22,000 ohms ±5%, 1/4 w.			-
	R24	3R152P433J	Composition: 43,000 ohms ±5%, 1/4 w.	1		SOCKETS
	R25	3R152P133J		XFL1	19A121920G3	Reed, mica-filled phen: 7 pins rated at 1 am at 500 VRMS with 4-1/2 inches of cable.
	R26	3R152P123J	Composition: 13,000 ohms ±5%, 1/4 w.			and an analysis of caste.
	R27		Composition: 12,000 ohms ±5%, 1/4 w.	A429		TONE REJECT FILTER 19C311797G2
im to		3R152P151J	Composition: 150 ohms ±5%, 1/4 w.			REV B
	R28	3R152P562J	Composition: 5600 ohms ±5%, 1/4 w.			gipigy-o
s	R29	3E152P513J	Composition: 51,000 ohms ±5%, 1/4 w.	C26	19A116080P206	
	R30	3R152P334J	Composition: 0.33 megohm ±5%, 1/4 w.	C27		Polyester: 0.068 μf ±5%, 50 VDCW.
	R31	3R152P104J	Composition: 0.1 megohm ±5%, 1/4 w.	and	19A116080P210	Polyester: 0.33 μf ±5%, 50 VDCW.
	R32	3R152P822J	Composition: 8200 ohms ±5%, 1/4 w.	C28		
	R33	19A116278P342	Metal film: 26,700 ohms ±2%, 1/2 w.	C29	19A116080P205	Polyester: 0.047 µf ±5%, 50 VDCW.
	R34	19A116278P233	Metal film: 2150 ohms ±2%, 1/2 w.			
	R35	19A116278P365	Metal film: 46,400 ohms ±2%, 1/2 w.	<b>J</b> 6	4033513P4	Contact, electrical; sim to Bead Chain 193-3.
	R36	19A116278P301	Metal film: 10,000 ohms ±2%, 1/2 w.	and J7		to bead chain 193-3.
	R37	19A116278P65	Metal film: 46.4 ohms ±2%, 1/2 w.			
ŀ	R38	3R152P204J	Composition: 0.2 megohm ±5%, 1/4 w.	L1	19A115690P1	
s	R39	19A116278P385	Metal film: 75,000 ohms ±2%, 1/2 w.		19411309021	Coil, RF: 880 mh ±5%, sim to Artted AC5672.
ain L93-3.	R40	19A116278P329	Metal film: 19,000 ohms ±2%, 1/2 w.			
	R41	19A116278P285	Metal film: 7500 ohms ±2%, 1/2 w.	R59*	3R152P182J	Composition: 1800 ohms ±5%, 1/4 w.
	R42	19A116278P412	Metal film: 130,000 ohms ±2%, 1/2 w.			In REV A and earlier:
ed AC5672.	R43	19A116278P269	Metal film: 5110 ohms ±2%, 1/2 w.		3R152P432J	Composition: 4300 ohms ±5%, 1/4 w.
	R44	19A116278P117	· · · · · · · · · · · · · · · · · · ·			200, 1714.
	R45	3R152P102J	Metal film: 147 ohms ±2%, 1/2 w.	A432 thru		OSCILLATOR/MULTIPLIER BOARD A432 19C311726G1
	and R46	3R132P1023	Composition: 1000 ohms ±5%, 1/4 w.	A435		A433 19C311726G2
ļ	R46			(		A434 19C311726G3 A435 19C311726G4
		ł	NOTE The value of Resistor R47 must be obtained from			
			the component, then find corresponding value in parts list for the correct part number.		E4044015115	
Į	R47A	3R152P822J	Composition: 8200 ohms ±5%, 1/4 w.	Cl thru	5494481P112	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
ľ	R47B	3R152P912J	Composition: 9100 ohms ±5%, 1/4 w.	C3		-

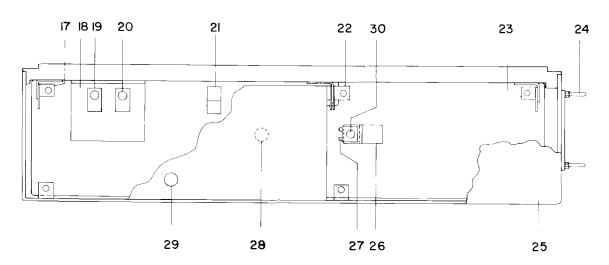
# LBI-3999

Cont'd from Page 11 (LBI-4021

MBOL	GE PART NO.	DESCRIPTION	SYMBDL	GE PART NO.	DESCRIPTION
R23	3R77P104K	Composition: 0.10 megohm ±10%, 1/2 w.	R54	3R77P822J	Composition: 8200 ohms ±5%, 1/2 w.
R24	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.	R55	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
R25	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.	R57	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
and R26			R58	3R77P181K	Composition: 180 ohms $\pm 10\%$ , $1/2$ w.
R27	3R77P753J	Composition: 75,000 ohms ±5%, 1/2 w.	R59	3R77P393K	Composition: 39,000 ohms ±10%, 1/2 w.
and R28		composition. To,000 onnus gow, 1/2 w,	R60	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
R29	3R77P182J	0	and R61		, , , , , , , , , , , , , , , , , , , ,
	_	Composition: 1800 ohms ±5%, 1/2 w.	R62*	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w. D
R30*	3R77P821J	Composition: 820 ohms ±5%, 1/2 w.			by REV C.
		In REV C and earlier:			Earlier than REV A:
	3R77P102J	Composition: 1000 ohms ±5%, 1/2 w.		3R77P223K	Composition: 22,000 ohms ±10%, 1/2 w.
R31	3R77P821J	Composition: 820 ohms ±5%, 1/2 w.	R63*	3R77P432J	Composition: 4300 ohms ±5%, 1/2 w. Del-
R32*	3R77P752J	Composition: 7500 ohms ±5%, 1/2 w. Deleted by REV A.		0-0501001	by REV A.
R33*	3R77P912J	Composition: 9100 ohms ±5%, 1/2 w.	R64*	3R77P120J	Composition: 12 ohms ±5%, 1/2 w.
		Earlier than REV A:			Earlier than REV C:
	3R77P203J			3R77P180J	Composition: 18 ohms ±5%, 1/2 w.
R34		Composition: 20,000 ohms ±5%, 1/2 w.	R65*	3R77P154K	Composition: 0.15 megohm ±10%, 1/2 w. : by REV B.
	3R77P332K	Composition: 3300 ohms ±10%, 1/2 w.	R66	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.
R35	3R77P330K	Composition: 33 hms ±10%, 1/2 w.	R70	3R77P184J	Composition: 0.18 megohm ±5%, 1/2 w.
R36	3R77P681J	Composition: 680 ohms ±5%, 1/2 w.	R75*	3R77P473J	
R37*	3R77P822J	Composition: 8200 ohms ±5%, 1/2 w. Deleted by REV A.	R/5*	SRIIPEISJ	Composition: 47,000 ohms ±5%, 1/2 w. AcREV A. Deleted by REV C.
R38*	3R77P752J	Composition: 7500 ohms $\pm 5\%$ , $1/2$ w.	R76*	3R77P912J	Composition: 9100 ohms ±5%, 1/2 w. Adde REV A. Deleted by REV C.
		Earlier than REV A:	R77*	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.
	3R77P622J	Composition: 6200 ohms ±5%, 1/2 w.			Earlier than REV C:
R39*	3R77P820J	Composition: 82 ohms ±5%, 1/2 w.		3R152P562J	Composition: 5600 ohms ±5%, 1/4 w. Add
		Earlier than REV A:	1		REV A.
	3R77P131J	Composition: 130 ohms ±5%, 1/2 w.	R78*	3R77P200J	Composition: 20 ohms ±5%, 1/2 w.
R40	3R77P241J	Composition: 240 ohms ±5%, 1/2 w.			In REV A, B, and C:
R41*	3R152P240J	Composition: 24 ohms ±5%, 1/4 w.		3R77P100J	Composition: 10 ohms ±5%, 1/2 w.
		Earlier than REV A:	R79*	3R152P393J	Composition: 39,000 ohms ±5%, 1/4 w. A by REV A.
	3R77P300J	Composition: 30 ohms ±5%, 1/2 w.	R80*	3R152P432J	Composition: 4300 ohms ±5%, 1/4 w. Add
R42*	3R77P200J	Composition: 20 ohms ±5%, 1/2 w.			by REV C.
		Earlier than REV A:	R81*	3R152P472J	Composition: 4700 ohms ±5%, 1/4 w. Add by REV C.
0.40	3R77P160J	Composition: 16 ohms ±5%, 1/2 w.	R82*	3R77P273J	Composition: 27,000 ohms ±5%, 1/2 w. Aby REV C.
R43	19B209358P101	Variable, carbon film: approx 25 to 250 ohms ±10%, 0.2 w; sim to CTS Type X-201.	R84*	3R77P2O3J	Composition: 20,000 ohms ±5%, 1/2 w. A
R44	19B209022P101	Wirewound: 0.27 ohms ±105%, 2 w; sim to 1RC Type BWH.			by REV E.
R45	3R77P123J	Composition: 12,000 ohms ±5%, 1/2 w.			
R46	3R77P913J	Composition: 91,000 ohms ±5%, 1/2 w.	RT1	5490828P41	Thermistor: 30 ohms ±10%, color code bl
R48*	19A116278P249	Metal film: 3160 ohms ±2%, I/2 w.		6 40000	white; sim to Globar Type B1211H-4.
	15	i i	RT2	5490828P9	Thermistor: 10,000 ohms $\pm 10\%$ , color cod yellow; sim to Globar Type $551H-8$ .
	3R77P302J	Earlier than REV B:	RT3*	5490828P9	Thermistor: 10.000 ohms ±10% color cod
	3877P302J	Composition: 3000 ohms ±5%, 1/2 w.		]	yellow; sim to Globar Type 551H-8. Adder
	anggeree	Earlier than REV A:			
	3R77P332J	Composition: 3300 ohms ±5%, 1/2 w.			
R49	3R77P103J	Composition: 10,000 ohms ±5%, I/2 w.	T1	19A116040P1	Audio freq: 300 to 4000 Hz,
R50	3R77P222J	Composition: 2200 ohms ±5%, 1/2 w.		]	Pri: 19.3 ohms ±10% DC res, Sec: 23.5 ohms ±10% DC res.
R51	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.	A428		
R52	3R77P682J	Composition: 6800 ohms ±5%, 1/2 w.	A428		ENCODER/DECODER 4EK16A10
R53*	3R77P303J	Composition: 30,000 ohms ±5%, 1/2 w. Deleted		1	
		by REV E.	Cl	19A116080P9	Polyester: 0.22 µf ±20%, 50 VDCW.
		In REV A, B:	C2	19A116080P205	Polyester: 0.047 µf ±5%, 50 VDCW.
	3R77P473J	Composition: 47,000 ohms ±5%, 1/2 w.	and C3	]	System. Store ht 13%, 50 VBCW.
	1	Earlier than REV A:	C4	19A116080P207	Palveston, A 1 of 15% to the
	3R77P3O3J	Composition: $30,000$ ohms $\pm 5\%$ , $1/2$ w.	~	1931100607207	Polyester: 0.1 μf ±5%, 50 VDCW.



VIEW "A"



406-470 MHZ RECEIVER 4ER42EIO-33 4ER42GIO-33

RC-1823A

Changes in the eq a "Revision Lette to the Parts List

# CHANNEL GUARD ENG

Rev. A - To obtai

# CHASSIS & RF ASSE

Rev. A - To facil Changed

Rev. B - To incor

Rev. C - To incor Ql. Add

# PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped on the unit includes all previous revisions. Refer to the Parts List for description of parts affected by these revisions.

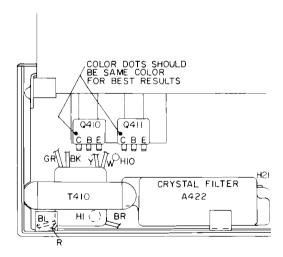
#### CHANNEL GUARD ENCODER/DECODER MODEL 4EK16A10

Rev. A - To obtain correct output level. Changed R8.

#### CHASSIS & RF ASSEMBLY 19E500881-G1 thru -G4

- Rev. A To facilitate tuning of low IF and improve critical squelch. Added C439 and C440. Changed C6 & C8 on A413/A414.
- Rev. B To incorporate new PA transistors. Changed Q410 and Q411. Added R411.

#### Outline Diagram Was:



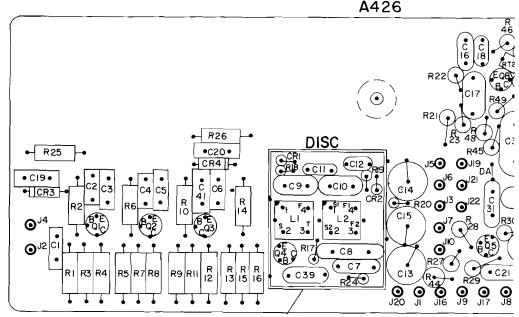
Rev. C - To incorporate a new multiplier transistor and decouple supply voltage. Changed Ql. Added Cl5 and R7.

#### IF AUDIO & SQUELCH BOARD A426 (19D413129-G3)

Rev. A - To make IF Audio & Squelch board compatible with new PA squelch operation. Deleted C24, C28, C29, C42, C43, R3: C49-C54, CR8, R75-R79 and RT3. Changed C21, C26, C37, R42, R48, R53 and R62.

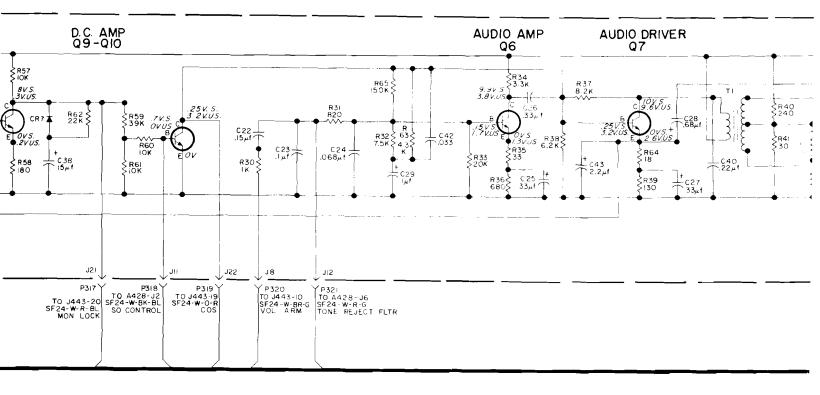
Outline Diagram Was:

# IF-AUDIO & SQUELCH BOARD



# Schematic Diagram Was:

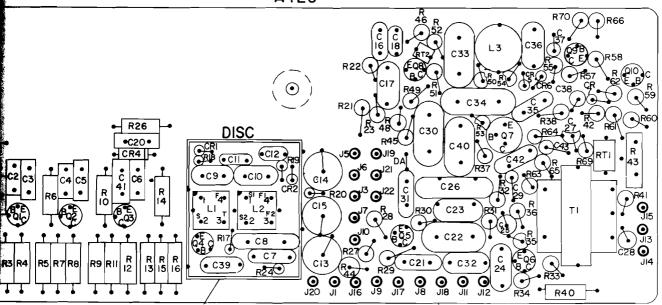
IF AUDIO & SQUELCH BOARD A426



To make IF Audio & Squelch board compatible with new PA transistors and to improve squelch operation. Deleted C24, C28, C29, C42, C43, R32, R37, R63 and R65. Added C49-C54, CR8, R75-R79 and RT3. Changed C21, C26, C37, C38, C40, R33, R38, R39, R41 R42, R48, R53 and R62.

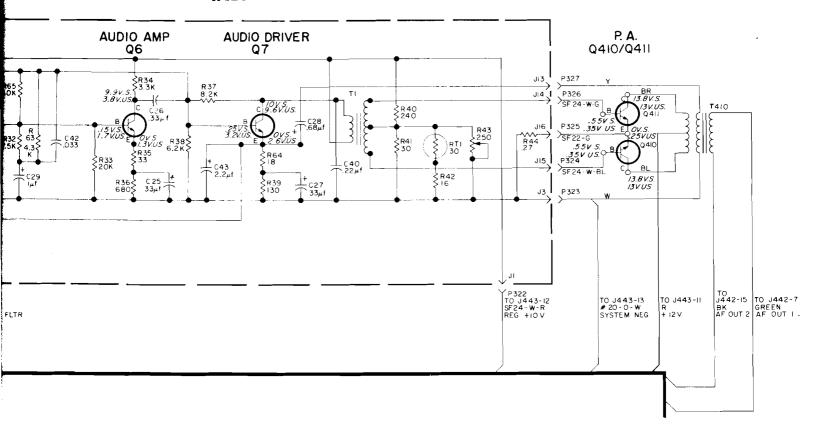
Outline Diagram Was:

# IF-AUDIO & SQUELCH BOARD A426



# Schematic Diagram Was:

# IF AUDIO & SQUELCH BOARD A426



# PRODUCTION CHANGES

406—470 MHz MASTR RECEIVER MODELS 4ER42E10-33 & 4ER42G10-33

Issue 6

#### ARD A426 (19D413129-G3)

ove receiver frequency response. R30 and R78.

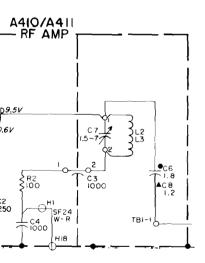
d Encoder/Decoder A428 (Model 4EK16A10) Filter A429 (19C311797-G2)

xcessive roll-off at 300 Hertz.

#### 7 19E500881-G1 THRU -G4

tze the R.F. Amplifier and to improve and tuning of the multiplier assembly. The R.F. amplifier board. Changed C5, on the multiplier assembly.

Diagram was:



# OARD A426 (19D413129-G3

e critical squelch action. 53 and added R84.

sate for vendor change. 26.

orate silicon diodes. R3 and CR4.

squelch action at  $-30^{\circ}$  C.

## CHASSIS & RF ASSEMBLY 19E500881-G2 and G4

REV. H - To improve band-end tuning. Changed C6 and C8.

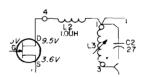
REV. J - To remove unnecessary protection.
Deleted CR1.

## CHASSIS & RF ASSEMBLY 19E500881-G1 and G3

REV. H - To remove unnecessary protection.
Deleted CR1.

REV. J - To prevent oscillations in the high IF amplifier and mixer. Changed C2 on the IF amplifier assembly 19B216356G1 & G2. Added C8 to First Mixer assembly 19C311974G1 as part of L3.

SCHEMATIC WAS:



REV. K - To incorporate a new transistor. Changed Q410 and Q411.

## CHASSIS & RF ASSEMBLY 19E500881-G2 and G4

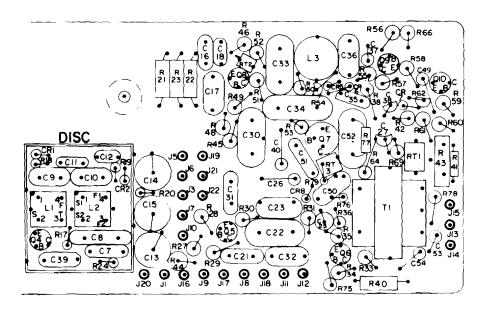
REV. L - To incorporate a new transistor. Changed Q410 and Q411.

# ) & SQUELCH BOARD A426 (19D413129-G3)

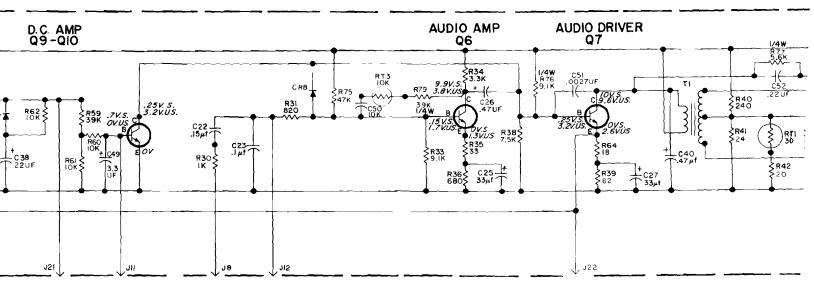
- v. B To control more closely the squelch control rotation. Changed R48.
- v. C To eliminate barely audible squelch switching transients and to reduce receiver squelch tail. Deleted C38, C49, CR7, CR8, R62, R75 and R76. Added C55, R80, R81, and R82. Changed C27, C36, R53, R64 and R77.

#### OUTLINE DIAGRAM WAS:

## IF-AUDIO & SQUELCH BOARD



## SCHEMATIC DIAGRAM WAS:



## LBI-3999

# CHANNEL GUARD ENCODER/DECODER MODEL 4EK16A10

- Rev. B To increase stop-band attenuation. Changed R8.
- Rev. C To optimize frequency response. Changed C29.

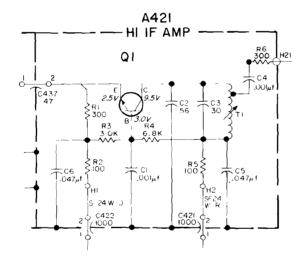
# TONE REJECT FILTER 19C311797-G2

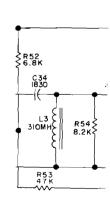
Rev. A - To optimize frequency response. Changed C29.

# CHASSIS & RF ASSEMBLY 19E500881-Gl thru -G4

- Rev. D To eliminate squelch opening thump in receivers with Channel Guard. Removed white-orange wire between J443-13 and TB2-1. Added a white-orange wire between P312 (on J17 on IF audio and squelch board) and TB2-1.
- Rev. E To stabilize the tripler stage. Removed C9 on A413/A414.
- Rev. F To improve sensitivity when used with dual front-end. Added C441. Changed DC feed point of R4 to C441-2. Jumpered C441-1 to C421-1.

# SCHEMATIC DIAGRAM WAS:





# **ORDERING SERVICE PARTS**

Each component appearing on the schematic diagram is identified by a symbol number, to simplify locating it in the parts list. Each component is listed by symbol number, followed by its description and GE Part Number.

Service parts may be obtained from Authorized GE Communication Equipment Service Stations or through any GE Radio Communication Equipment Sales Office. When ordering a part, be sure to give:

- GE Part Number for component
- 2.
- Description of part
  Model number of equipment 3.
- Revision letter stamped on unit 4.

These instructions do not purport to cover all details or variations in equipment nor to provide for every possible contingency to be met in connection with installation, operation or maintenance.

Should further information be desired, or should particular problems arise which are not covered sufficiently for the purchaser's purposes, contact the nearest Radio Communication Equipment Sales Office of the General Electric Company.

MOBILE RADIO DEPARTMENT
GENERAL ELECTRIC COMPANY ● LYNCHBURG, VIRGINIA 24502

